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(54) Organic light emitting diode display device and method of driving the same

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Description

BACKGROUND

FIELD OF THE DISCLOSURE

[0001] The present disclosure relates to an organic light emitting diode (OLED) display device and a method of driving the same, and more particularly, to an OLED display device and a method of driving the same, which may improve initialization characteristics to enhance response characteristics and solve luminance degradation.

DISCUSSION OF THE RELATED ART

[0002] In recent years, as the information age has progressed, various needs for display fields have increased. To meet those needs, research has been conducted into various flat panel display (FPD) devices that are fabricated to be ultrathin and lightweight and consume low power, for example, liquid crystal display (LCD) devices, plasma display panel (PDP) devices, and organic light emitting diode (OLED) devices.

[0003] An OLED display device is an emissive display including organic compounds formed on a transparent substrate to emit red (R), green (G), and blue (B) light. In general, the OLED display device may include an OLED panel and a driver circuit.

[0004] Thus, the OLED display device does not require an additional light source unlike an LCD device.

[0005] As a result, since a backlight unit (BLU) is not required, the OLED display device may be fabricated using a simpler process at lower fabrication cost than the LCD device, and has attracted much attention as an advanced FPD.

[0006] Furthermore, the OLED display device may have a wider viewing angle and a higher contrast ratio than the LCD device, be driven at a low direct-current (DC) voltage, have a high response speed, and be highly resistant to external shock and applicable within a wide temperature range.

[0007] In particular, in an active-matrix-type OLED (AMOLED) display device, a voltage for controlling current applied to a pixel region may be charged in a storage capacitor so that the voltage can be maintained until the next frame signal is applied. Thus, the AMOLED display device may be driven to maintain an emission state during display of one screen irrespective of the number of gate lines.

[0008] Accordingly, since the AMOLED display device exhibits the same luminance even with application of a low current, the AMOLED display device may reduce power consumption and be scaled up.

[0009] FIG. 1 is a schematic equivalent circuit diagram of a pixel region of a conventional OLED display device.

[0010] As shown in FIG. 1, in the conventional OLED display device, a gate line GL and a data line DL may be formed across each other to define a pixel region P, which

may include a switching transistor T_{sw}, a driver transistor T_{dr}, a storage capacitor C_{st}, and an OLED.

[0011] The switching transistor T_{sw} may be connected to the gate line GL, the data line DL, and one end of the storage capacitor C_{st}.

[0012] In addition, the driver transistor T_{dr} may be connected to one end of the storage capacitor C_{st}, the OLED, and the other end of the storage capacitor C_{st}.

[0013] In this case, the OLED and the driver transistor T_{dr} may be connected between a high-potential voltage line VDD and a low-potential voltage line VSS.

[0014] The operation of the pixel region of the OLED display device will now be described. To begin with, when the switching transistor T_{sw} is turned on by supplying a gate signal through the gate line GL, a data signal applied through the data line DL may be transmitted to the driver transistor T_{dr} and the storage capacitor C_{st}.

[0015] Also, when the driver transistor T_{dr} is turned on in response to the data signal, current may flow through the OLED so that the OLED can emit light.

[0016] In this case, intensity of light emitted by the OLED may be proportional to the amount of current flowing through the OLED, which may be proportional to the magnitude of the data signal.

[0017] Accordingly, the OLED display device may apply a data signal having various magnitudes to the respective pixel regions P to produce various grayscales. As a result, the OLED display can display images.

[0018] Furthermore, the storage capacitor C_{st} may maintain the data signal during one frame so that the amount of current flowing through the OLED can be maintained constant, and a grayscale displayed by the OLED can be maintained constant.

[0019] Meanwhile, unlike a liquid crystal display (LCD) in which a transistor of a pixel region is turned on for only a relatively short time during one frame, in the OLED display device, the driver transistor T_{dr} may remain turned on for a relatively long time for which the OLED emits light to display a grayscale, so that the driver transistor T_{dr} can easily deteriorate.

[0020] As a result, a threshold voltage V_{th} of the driver transistor T_{dr} may vary. Variation in the threshold voltage V_{th} of the driver transistor T_{dr} may adversely affect the resolution of the OLED display device.

[0021] That is, the pixel region of the OLED display device may display different grayscales in response to the same data signal due to the variation in the threshold voltage V_{th} of the driver transistor T_{dr}, thereby exacerbating the resolution of the OLED display device.

[0022] Therefore, it is necessary to develop a new pixel structure of an OLED display device to compensate for a variation in threshold voltage caused by deterioration of a driver transistor.

[0023] WO2011/013409 A1 describes an organic EL display device having a compensation circuit. A pixel has seven transistors, two capacitors, and one OLED. A first transistor causes data signals stored in the capacitors to be discharged via a voltage-initializing-line and thereby

initializes the gate voltage of the drive transistor. The second transistor compensates for inaccuracy in the threshold voltage of the drive transistor. The third transistor switches on/off data signals. The drive transistor determines the amperage for supplying a current to the OLED in response to data signals input through the third transistor. The fifth transistor switches on/off a current supplied from a power-source line to the drive transistor in response to light-emitting signals input from a light-emission-controlling line. The sixth transistor switches on/off a current supplied from the drive transistor to the OLED in response to the light-emitting signals. The first capacitor stores a gate voltage input to the drive transistor. The second capacitor assists the first capacitor. The OLED emits light in response to a current supplied from the drive transistor. The anode of the OLED is coupled with a drain of the sixth transistor. The source electrode and the drain electrode of the seventh transistor are connected in parallel to the OLED, in order to enable discharge of charge, which is stored in a parasitic capacitance between the gate electrode of the drive transistor and the anode of the OLED.

[0024] US 2010/0164847 A1 describes a similar display device, in which the anode voltage of an organic light emitting element is periodically reset. A switching transistor resets the anode voltage to a reset voltage.

[0025] US 2008/0150846 A1 describes a further similar organic light emitting display having an initial switching transistor, coupled between a storage capacitor and an initial power source line, for initializing the storage capacitor, and having a switching transistor, coupled to the initial power source line, for applying a reverse bias voltage to an OLED.

SUMMARY OF THE INVENTION

[0026] The present invention is directed to an organic light emitting diode (OLED) display device and a method of driving the same that substantially obviates one or more of the problems due to limitations and disadvantages of the related art.

[0027] Additional features and advantages of the invention will be set forth in the description which follows, and in part will be apparent from the description, or may be learned by practice of the invention. The objectives and other advantages of the invention will be realized and attained by the structure particularly pointed out in the written description and claims hereof as well as the appended drawings.

[0028] To achieve these and other advantages and in accordance with the purpose of the present invention, as embodied and broadly described herein, an OLED display device includes: a first transistor connected to a high-potential voltage terminal and a second node; a switching transistor connected to a data line and the second node; a second transistor connected to a drain electrode of a driver transistor and a first node; an emission control transistor connected to the drain electrode of the driver tran-

sistor and one electrode of an OLED; a third transistor connected to the one electrode of the OLED and configured to reduce a voltage applied to the one electrode of the OLED; and a first capacitor connected between the high-potential voltage terminal and the first node.

[0029] In another aspect, a method of driving an OLED display device including a switching transistor, a driver transistor, an emission control transistor, first and second capacitors, and an OLED, the method includes: initializing a first node to which a gate electrode of the driver transistor is connected, during turn-on operations of the second and third transistors and the emission control transistor; sensing a threshold voltage of the driver transistor, and transmitting a data voltage to the first node during turn-on operations of the switching transistor and the second and third transistors; and allowing the OLED to emit light during a turn-on operation of the emission control transistor.

[0030] It is to be understood that both the foregoing general description and the following detailed description are exemplary and explanatory and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0031] The accompanying drawings, which are included to provide a further understanding of the invention and are incorporated in and constitute a part of this specification, illustrate embodiments of the invention and together with the description serve to explain the principles of the invention. In the drawings:

FIG. 1 is a schematic equivalent circuit diagram of a pixel region of a conventional organic light emitting diode (OLED) display device;

FIG. 2 is a schematic diagram of an OLED display device according to an embodiment of the present invention;

FIG. 3 is a schematic equivalent circuit diagram of a pixel region of an OLED display device according to a first embodiment of the present invention;

FIG. 4 is a timing diagram of a plurality of control signals applied to the OLED according to the first embodiment of the present invention;

FIG. 5 is a reference diagram for explaining an operation of the pixel region of the OLED display device according to the first embodiment of the present invention;

FIG. 6 is a schematic equivalent circuit diagram of a pixel region of an OLED display device according to a second embodiment of the present invention;

FIG. 7 is a timing diagram of a plurality of control signals applied to the OLED display device according to the second embodiment of the present invention, voltages of first and second nodes, and current flowing through an emission diode;

FIG. 8 is a reference diagram for explaining an operation of the pixel region of the OLED display device

according to the second embodiment of the present invention;

FIG. 9 is a schematic equivalent circuit diagram of a pixel region of an OLED display device according to a third embodiment of the present invention;

FIG. 10 is a schematic equivalent circuit diagram of a pixel region of an OLED display device according to a fourth embodiment of the present invention;

FIG. 11 is a timing diagram of a plurality of control signals applied to the OLED display devices according to the first and fourth embodiments of the present invention;

FIGS. 12A and 12B are reference diagrams for explaining initialization characteristics of the OLED display device according to the first embodiment of the present invention; and

FIGS. 13A and 13B are reference diagrams for explaining initialization characteristics of the OLED display device according to the second embodiment of the present invention.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0032] Reference will now be made in detail to the preferred embodiments, examples of which are illustrated in the accompanying drawings.

[0033] FIG. 2 is a schematic diagram of an organic light emitting diode (OLED) display device according to an embodiment of the present invention, and FIG. 3 is a schematic equivalent circuit diagram of an OLED display device according to a first embodiment of the present invention.

[0034] As shown in FIG. 2, an OLED display device 100 according to the present invention may include a display panel 110 configured to display images, a source driver 120, a scan driver 130, and a timing controller 140 configured to control a driving time point of each of the source driver 120 and the scan driver 130.

[0035] The display panel 110 may include a plurality of scan lines SCL1 to SCLm and a plurality of data lines DL1 to DLn, which may intersect one another to define a plurality of pixel regions P, and a plurality of emission control lines EL1 to ELm.

[0036] Since the respective pixel regions P have the same configuration, the plurality of scan lines SCL1 to SCLm, the plurality of data lines DL1 to DLn, and the plurality of emission control lines EL1 to ELm will be respectively described as scan lines SCL, data lines DL, and emission control lines EL for brevity.

[0037] As shown in FIG. 3, a switching transistor Tsw, a driver transistor Tdr, an emission control transistor Tem, first through third transistors T1 to T3, a first capacitor C1, and an OLED may be formed in each of the pixel regions P.

[0038] Although FIG. 3 shows an example in which the switching transistor Tsw, the driver transistor Tdr, the emission control transistor Tem, and the first through

third transistors T1 to T3 are P-type transistors, the present invention is not limited thereto. For example, the switching transistor Tsw, the driver transistor Tdr, the emission control transistor Tem, and the first through third transistors T1 to T3 may be N-type transistors.

[0039] Source and gate electrodes of the switching transistor Tsw may be connected to the data line DL and the scan line SCL, respectively, and a drain electrode of the switching transistor Tsw may be connected to a second node N2.

[0040] The switching transistor Tsw may be turned on in response to a scan signal applied through the scan line SCL, and apply a data voltage Vdata to the second node N2.

[0041] Source and gate electrodes of the driver transistor Tdr may be connected to the second node N2 and a first node N1, respectively, and a drain electrode of the driver transistor Tdr may be connected to a third node N3.

[0042] In other words, the first node N1 may be a node to which the gate electrode of the driver transistor Tdr is connected, the second node N2 may be a node to which the source electrode of the driver transistor Tdr is connected, and the third node N3 may be a node to which the drain electrode of the driver transistor Tdr is connected.

[0043] The driver transistor Tdr may serve to control the amount of current flowing through the OLED. The amount of current flowing through the OLED may be proportional to the magnitude of the data voltage Vdata applied to the gate electrode of the driver transistor Tdr.

[0044] That is, the OLED display device 100 may apply the data voltage Vdata having various magnitudes to the respective pixel regions P, and display different gray-scales to display images.

[0045] Source and gate electrodes of the emission control transistor Tem may be connected to the third node N3 and the emission control line EL, respectively, and a drain electrode of the emission control transistor Tem may be connected to one electrode of the OLED.

[0046] The emission control transistor Tem may be turned on in response to an emission control signal applied through the emission control line EL, and control an emission time point of the OLED.

[0047] Source and gate electrodes of the first transistor T1 may be connected to a terminal of a high-potential voltage Vdd and the emission control line EL, respectively, and a drain electrode of the first transistor T1 may be connected to the second node N2.

[0048] The first transistor T1 may be turned on in response to an emission control signal Em applied through the emission control line EL, and apply a high-potential voltage Vdd to the second node N2.

[0049] In this case, the high-potential voltage Vdd may be, for example, about 5V.

[0050] Source and gate electrodes of the second transistor T2 may be connected to the third node N3 and the scan line SCL, respectively, and a drain electrode of the second transistor T2 may be connected to the first node

N1.

[0051] The second transistor T2 may be turned on in response to a scan signal applied through the scan line SCL, and initialize the first node N1 to a reference voltage applied through a reference voltage line VL.

[0052] Source and gate electrodes of the third transistor T3 may be connected to a drain electrode of the emission control transistor Tem and the scan line SCL, (respectively), and a drain electrode of the third transistor T3 may be connected to the reference voltage line VL.

[0053] The third transistor T3 may be turned on in response to the scan signal applied through the scan line SCL, and apply the reference voltage to an anode electrode of the OLED.

[0054] Thus, a current path may be formed from the drain electrode of the third transistor T3 to the reference voltage line VL during a turn-on operation of the third transistor T3 so that current flowing into the OLED can be reduced.

[0055] The first capacitor C1 may be connected between the first node N1 and the source electrode of the first transistor T1, and store a voltage difference between a voltage of the first node N1 and a voltage applied to the source electrode of the first transistor T1.

[0056] The first capacitor C1 may be a storage capacitor, which may maintain a data voltage during one frame so that the amount of current flowing through the OLED can be maintained constant, and a grayscale displayed by the OLED can be maintained constant.

[0057] The anode electrode of the OLED may be connected to the drain electrode of the emission control transistor Tem, and a cathode electrode thereof may be connected to a terminal of a low-potential voltage Vss.

[0058] In this case, the low-potential voltage Vss may be, for example, -5V.

[0059] Referring back to FIG. 2, the source driver 120 may include at least one driver integrated circuit (IC) (not shown) configured to supply the data signal to the display panel 110.

[0060] The source driver 120 may receive converted image signals (red/green/blue (R/G/B)) and a plurality of data control signals from the timing controller 140, generate the data signal using the converted image signals (R/G/B) and the plurality of data control signals, and apply the generated signal to the display panel 110 through the data line DL.

[0061] The timing controller 140 may receive a plurality of control signals, such as a plurality of image signals, a vertical synchronous signal Vsync, a horizontal synchronous signal Hsync, and a data enable signal DE, through an interface from a system, such as a graphic card.

[0062] The timing controller 140 may generate the plurality of data signals, and apply the data signals to respective driver ICs of the source driver 120.

[0063] The scan driver 130 may generate the scan signal using the control signal received from the timing controller 140, and supply the generated scan signal through the scan line SCL to the display panel 110.

[0064] Furthermore, although FIG. 2 illustrates that the scan driver 130 applies an emission control signal through the emission control line EL to the display panel 110, the present invention is not limited thereto. For example, an additional emission control driver configured to apply the emission control signal may be formed in the OLED display device 100 according to the present invention.

[0065] Hereinafter, an operation of the pixel region P of the OLED display device 100 will be described.

[0066] FIG. 4 is a timing diagram of a plurality of control signals applied to the OLED display device 100 according to the first embodiment of the present invention, and FIG. 5 is a reference diagram for explaining the operation of the pixel region of the OLED display device 100 according to the first embodiment of the present invention.

[0067] As shown in FIG. 4, a low-level scan signal Scan and a low-level emission control signal Em may be applied during a first time t1.

[0068] In this case, the voltage level of a reference voltage supplied through the reference voltage line VL may be set such that a voltage difference between the reference voltage and the low-potential voltage Vss is lower than the threshold voltage Vth of the OLED.

[0069] Here, the threshold voltage Vth of the OLED may be, for example, 2V.

[0070] In addition, the voltage level of the reference voltage may be set to be lower than a voltage difference 'Vdata-Vth' between the data voltage Vdata and the threshold voltage Vth of the driver transistor Tdr.

[0071] In this case, the reference voltage may be, for example, -4V.

[0072] Thus, the switching transistor Tsw and the second and third transistors T2 and T3 may be turned on in response to a low-level scan signal Scan, and the emission control transistor Tem and the first transistor T1 may be turned on in response to the emission control signal Em and initialize the first node N1 to the reference voltage.

[0073] In other words, during the first time t1, the switching transistor Tsw, the emission control transistor Tem, and the first through third transistors T1 to T3 may be turned on, and the driver transistor Tdr may also be turned on in response to a data voltage of the previous frame stored in the first capacitor C1.

[0074] As the second transistor T2, the emission control transistor Tem, and the third transistor T3 are simultaneously turned on, an initialization current path may be formed from the first node N1 to the reference voltage line VL.

[0075] As a result, the first node N1 may be initialized to the reference voltage during the first time t1.

[0076] In addition, due to the formation of the initialization current path, current flowing into the OLED may be reduced, thereby preventing the OLED from emitting light.

[0077] During the first time t1, a voltage VN1 applied to the first node N1 may be the reference voltage, while

a voltage VN2 applied to the second node N2 may be the high-potential voltage Vdd.

[0078] A low-level scan signal Scan and a high-level emission control signal Em may be applied during a second time t2.

[0079] As a result, the switching transistor Tsw and the second and third transistors T2 and T3 may be turned on in response to a low-level scan signal Scan, and sense the threshold voltage Vth of the driver transistor Tdr.

[0080] Furthermore, the data voltage Vdata may be applied to the first node N1 along a sampling/writing current path from the second node N2 to the first node N1, which may be formed by turning on the switching transistor Tsw.

[0081] During the second time t2, a voltage VN1 applied to the first node N1 may be 'Vdata-Vth', and a voltage VN2 applied to the second node N2 may be 'Vdata'.

[0082] The threshold voltage Vth of the driver transistor Tdr and the data voltage Vdata may be stored in the first capacitor C1 during the second time t2.

[0083] Here, the emission control transistor Tem and the first transistor T1 may be turned off.

[0084] During a third time t3, a high-level scan signal Scan may be applied, and the emission control signal Em may be applied during the high-to-low transition thereof.

[0085] As a result, the emission control transistor Tem, the first transistor T1, and the driver transistor Tdr may be turned on, so that an emission current path can be formed from the second node N2 to the OLED. Also, current IOLED may be supplied to the OLED along the emission current path to enable an emission state.

[0086] Here, the switching transistor Tsw and the second and third transistors T2 and T3 may remain turned off.

[0087] During the third time t3, a voltage VN1 applied to the first node N1 may be 'Vdata-Vth', and a voltage VN2 applied to the second node N2 may be 'Vdd'.

[0088] In this case, the current IOLED flowing through the OLED may be defined as in Equation 1:

$$I_{OLED} = k \cdot (V_{dd} - V_{data})^2 \quad (1),$$

wherein k is a proportional constant determined by the structure and physical properties of the driver transistor Tdr, for example, the mobility of the driver transistor Tdr and a ratio W/L of a channel width W of the driver transistor Tdr to a channel length L thereof.

[0089] As a result, current IOLED supplied to the OLED for the third time t3 may be irrelevant to the threshold voltage Vth of the driver transistor Tdr, and may be determined by the high-potential voltage Vdd and the data voltage Vdata.

[0090] Thus, non-uniformity in luminance caused by differences between the characteristics of transistors may be improved.

[0091] In the OLED display device according to the first embodiment of the present invention, an initialization period for initializing the first node N1 to a predetermined voltage may be needed so that the driver transistor Tdr cannot be affected by the data voltage of the previous frame due to operating characteristics of a threshold voltage (Vth) compensating circuit of the driver transistor Tdr.

[0092] Thus, a pixel structure of the OLED display device according to the first embodiment of the present invention may include the third transistor T3, which may allow current supplied to the OLED to flow into the reference voltage line VL during the first time t1, which is an initialization period, and the first node N1 may be initialized to the reference voltage, which is an initialization voltage, during the first time t1.

[0093] However, not only the second and third transistors T2 and T3 but also the switching transistor Tsw and the first transistor T1 may remain turned on during the first time t1.

[0094] Accordingly, as shown in FIG. 5, first through third current paths may be formed from the second node N2 toward the switching transistor Tsw, the first transistor T1, and the driver transistor Tdr, respectively.

[0095] In other words, the first current path may be formed from the second node N2 toward the switching transistor Tsw, the second current path may be formed from the second node N2 toward the first transistor T1, and the third current path may be formed from the second node N2 toward the driver transistor Tdr.

[0096] As a result, since a high initialization current flows along an initialization current path from the first node N1 to the reference voltage line VL and the third current path, which are formed during the first time t1, the first node N1 may not be initialized to the reference voltage, which is the initialization voltage.

[0097] Also, as the switching transistor Tsw and the first transistor T1 are turned on, an electrical short between the high-potential voltage Vdd and the data voltage Vdata may occur to generate overcurrent.

[0098] In an example, a high initialization current may flow along the initialization current path from the first node N1 to the reference voltage line VL and the third current path, which are formed during the first time t1.

[0099] In this case, the high-potential voltage Vdd and the low-potential voltage Vss may be 5 V and -5 V, respectively, and the reference voltage may be -4 V.

[0100] Also, with application of the high initialization current, voltage division may occur due to on-resistances Ron of the emission control transistor Tem and the third transistor T3.

[0101] In this case, a voltage of -2.8 V may be applied to a node connected to an anode electrode of the OLED, and a voltage of -2 V may be applied to each of the first and third nodes N1 and N3.

[0102] Accordingly, in the pixel structure of the OLED display device according to the first embodiment of the present invention, the first node N1 cannot be initialized to the reference voltage, which is the initialization voltage,

during the initialization period.

[0103] As a result, in the pixel structure of the OLED display device according to the first embodiment of the present invention, attained luminance and capability of compensating for a deviation in the threshold voltage V_{th} of the driver transistor T_{dr} may depend on the data voltage V_{data} .

[0104] In particular, attainment of desired luminance and capability of compensating for a deviation in the threshold voltage V_{th} of the driver transistor T_{dr} may be degraded at a low data voltage V_{data} .

[0105] For example, when the data voltage V_{data} is about 3V and a threshold voltage V_{th} of the driver transistor T_{dr} ranges from about -2 V to about -4 V, grayscale expression and compensation of the threshold voltage V_{th} may be normally enabled.

[0106] In contrast, when the data voltage V_{data} is about 1V and the threshold voltage V_{th} of the driver transistor T_{dr} is about -3 V or less, grayscale expression and the compensation of the threshold voltage V_{th} cannot be normally enabled.

[0107] That is, when the data voltage V_{data} is maintained constant, as the threshold voltage V_{th} of the driver transistor T_{dr} decreases, attainment of desired luminance and capability of compensating for a deviation in the threshold voltage V_{th} of the driver transistor T_{dr} may further deteriorate.

[0108] In addition, when the threshold voltage V_{th} of the driver transistor T_{dr} is maintained constant, as the data voltage V_{data} decreases, attainment of desired luminance and capability of compensating for a deviation in the threshold voltage V_{th} of the driver transistor T_{dr} may further deteriorate.

[0109] Accordingly, when the data voltage V_{data} or the threshold voltage V_{th} of the driver transistor is reduced, the voltage level of the reference voltage should be further dropped to normally sample (or sense) the threshold voltage V_{th} of the driver transistor T_{dr} .

[0110] However, in the pixel structure of the OLED display device according to the first embodiment of the present invention, since overcurrent occurs due to an electrical short between the high-potential voltage V_{dd} and the data voltage V_{dd} during the initialization period, even if the voltage level of the reference voltage is further reduced, the first node $N1$ cannot be initialized to the reference voltage, which is the initialization voltage.

[0111] As a result, when the pixel structure of the OLED display device according to the first embodiment of the present invention is applied, there are specific limits to attaining desired luminance and improving capability of compensating for a deviation in the threshold voltage V_{th} of the driver transistor T_{dr} .

[0112] FIG. 6 is a schematic equivalent circuit diagram of a pixel region of an OLED display device according to a second embodiment of the present invention. Since some components of the OLED display device according to the second embodiment are substantially the same as in the first embodiment, differences between the first and

second embodiments will now be chiefly described.

[0113] As shown in FIG. 6, a switching transistor T_{sw} , a driver transistor T_{dr} , an emission control transistor T_{em} , first through third transistors $T1$ to $T3$, a first capacitor $C1$, a second capacitor $C2$, and an OLED may be formed in each of pixel regions.

[0114] In a pixel structure of the OLED display device according to the second embodiment of the present invention, a connection structure among first through third transistors $T1$ to $T3$ may be modified.

[0115] Source and gate electrodes of the first transistor $T1$ may be connected to a terminal of a high-potential voltage V_{dd} and an initialization line IL , respectively, and a drain electrode of the first transistor $T1$ may be connected to a second node $N2$.

[0116] The first transistor $T1$ may be turned on in response to an initialization signal applied through the initialization line IL , and apply the high-potential voltage V_{dd} to the second node $N2$. In this case, the high-potential voltage V_{dd} may be, for example, about 5 V.

[0117] Source and gate electrodes of the second transistor $T2$ may be connected to a third node $N3$ and a sensing line SEL , respectively, and a drain electrode of the second transistor $T2$ may be connected to a first node $N1$.

[0118] The second transistor $T2$ may be turned on in response to a sensing signal applied through the sensing line SEL , and apply a reference voltage to the first node $N1$ to initialize the first node $N1$.

[0119] Source and gate electrodes of the third transistor $T3$ may be connected to a drain electrode of the emission control transistor T_{em} and the sensing line SEL , respectively, and a drain electrode of the third transistor $T3$ may be connected to a reference voltage line VL .

[0120] The third transistor $T3$ may be turned on in response to the sensing signal applied through the sensing line SEL , and apply the reference voltage to an anode electrode of the OLED.

[0121] The first capacitor $C1$ may be connected between the first node $N1$ and the source electrode of the first transistor $T1$, and store a voltage difference between a voltage of the first node $N1$ and a voltage applied to the source electrode of the first transistor $T1$.

[0122] The first capacitor $C1$ may be a storage capacitor configured to maintain a data voltage during one frame so that the amount of current flowing through the OLED can be maintained constant, and a grayscale displayed by the OLED can be maintained constant.

[0123] The second capacitor $C2$ may be connected between the first node $N1$ and the sensing line SEL , and store a voltage difference between the voltage of the first node $N1$ and the sensing signal.

[0124] The OLED display device according to the second embodiment of the present invention to which the above-described pixel structure is applied may further include an initialization driver configured to apply an initialization signal, and a sensing driver configured to apply a sensing signal.

[0125] That is, in the OLED display device according to the second embodiment of the present invention, control signals of respective transistors may be separated from one another by increasing the number of drivers.

[0126] FIG. 7 is a timing diagram of a plurality of control signals applied to the OLED display device according to the second embodiment of the present invention, voltages of first and second nodes, and current flowing through an emission diode, and FIG. 8 is a reference diagram for explaining an operation of the pixel region of the OLED display device according to the second embodiment of the present invention. Hereinafter, the operation of the pixel region of the OLED display device according to the second embodiment of the present invention will be described with reference to FIGS. 6 through 8.

[0127] As shown in FIG. 7, during an initialization time T_{ini} , a low-level sensing signal Sen and a low-level emission control signal Em may be applied, and a high-level scan signal $Scan$ and an initialization signal $Init$ may be applied.

[0128] In this case, the voltage level of a reference voltage applied through the reference voltage line VL may be set such that a voltage difference between the reference voltage and the low-potential voltage V_{ss} is lower than the threshold voltage V_{th} of the OLED.

[0129] Here, the threshold voltage V_{th} of the OLED may be, for example, about 2V.

[0130] In addition, the voltage level of the reference voltage may be set to be lower than a voltage difference between the data voltage V_{data} and the threshold voltage V_{th} of the driver transistor T_{dr} .

[0131] For example, the reference voltage may be about -4 V.

[0132] Accordingly, the second and third transistors T_2 and T_3 and the emission control transistor Tem may be turned on in response to the low-level sensing signal Sen and the low-level emission control signal Em , respectively, so that the first node N_1 can be initialized to the reference voltage.

[0133] That is, in the pixel structure of the OLED display device according to the second embodiment of the present invention, the switching transistor T_{sw} and the first transistor T_1 may remain turned off during the initialization time T_{ini} .

[0134] As a result, in the pixel structure of the OLED display device according to the second embodiment of the present invention, the flow of overcurrent caused by an electrical short between the high-potential voltage V_{dd} and the data voltage V_{data} may be prevented.

[0135] More specifically, as shown in FIG. 8, an initialization current path may be formed from the first node N_1 to the reference voltage line VL during the initialization time T_{ini} .

[0136] Also, the switching transistor T_{sw} and the first transistor T_1 may be turned off so that a voltage applied to the second node N_2 may be floated and dropped to about -2.4 V.

[0137] Thus, current flowing along a third current path

formed from the second node N_2 toward the driver transistor T_{dr} may be reduced so that an initialization current flowing along the initialization current path and the third current path can be reduced.

5 [0138] Also, due to the reduction in the initialization current, voltage division caused by on-resistances R_{on} of the emission control transistor Tem and the third transistor T_3 may be reduced.

10 [0139] In this case, when the duration of the initialization time T_{ini} is sufficient, a voltage of about -3.9 V may be applied to a node connected to an anode electrode of the OLED, and a voltage of about -3.8 V may be applied to the first and second nodes N_1 and N_3 .

15 [0140] Accordingly, in the pixel structure of the OLED display device according to the second embodiment of the present invention, the first node N_1 may be initialized to about -3.8 V, which is about equal to the reference voltage corresponding to the initialization voltage, during the initialization time T_{ini} .

20 [0141] In addition, a voltage of about -3.9 V may be applied to the node connected to the anode electrode of the OLED, so a voltage difference between a voltage of the node connected to the anode electrode of the OLED and the low-potential voltage V_{ss} may become lower than the threshold voltage V_{th} of the OLED to prevent the OLED from emitting light.

25 [0142] The voltage V_{N1} applied to the first node N_1 during the initialization time T_{ini} may be the reference voltage, and the voltage V_{N2} applied to the second node N_2 may be the high-potential voltage V_{dd} .

30 [0143] During a sensing time T_{sen} , a low-level sensing signal Sen and a high-level emission control signal Em may be applied, and a low-level scan signal $Scan$ and a high-level initialization signal $Init$ may be applied.

35 [0144] As a result, the switching transistor T_{sw} and the second and third transistors T_2 and T_3 may be turned on in response to the low-level sensing signal Sen and sense the threshold voltage V_{th} of the driver transistor T_{dr} .

40 [0145] Furthermore, a data voltage V_{data} may be applied to the first node N_1 along a sampling/writing current path from the second node N_2 to the first node N_1 , which is formed by turning on the switching transistor T_{sw} and the second transistor T_2 .

45 [0146] The voltage V_{N1} applied to the first node N_1 during the sensing time T_{sen} may be ' $V_{data}-V_{th}$ ' or less to enable a normal sampling (sensing) operation.

[0147] Also, the voltage V_{N2} applied to the second node N_2 may be ' V_{data} '.

50 [0148] During the sensing time T_{sen} , the threshold voltage V_{th} of the driver transistor T_{dr} and the data voltage V_{data} may be stored in the first capacitor C_1 .

[0149] Here, the emission control transistor Tem and the first transistor T_1 may be in a turn-off state.

55 [0150] During a holding time T_{hold} , the sensing signal Sen may be applied during the low-to-high transition thereof, the emission control signal Em may be applied during the high-to-low transition, the scan signal $Scan$

may be applied during the low-to-high transition thereof, and the initialization signal Init may be applied during the high-to-low transition thereof.

[0151] As a result, states of the switching transistor Tsw, the emission control transistor Tem, and the first through third transistors T1 to T3 may be changed.

[0152] More specifically, the switching transistor Tsw may be changed from a turn-on state to a turn-off state, the first transistor T1 may be changed from a turn-off state to a turn-on state, each of the second and third transistors T2 and T3 may be changed from a turn-on state to a turn-off state, and the emission control transistor Tem may be changed from a turn-off state to a turn-on state.

[0153] During the holding time T_hold, a sensing signal Sen applied to one end of the second capacitor C2 may make the low-to-high transition.

[0154] Thus, a voltage VN1 applied to the first node N1 may rise under the influence of a variation in voltage due to a coupling effect of the second capacitor C2.

[0155] Also, during the holding time T_hold, a voltage VN2 applied to the second node N2 may also rise under the influence of a variation in voltage applied to the first node N1.

[0156] In this case, in the pixel structure of the OLED display device according to the second embodiment of the present invention, the sum of the initialization time T_ini, the sensing time T_sen, and the holding time T_hold may be one horizontal period 1H.

[0157] During the emission time T_em, a high-level sensing signal Sen and a low-level emission control signal Em may be applied, and a high-level scan signal Scan and a low-level initialization signal Init may be applied.

[0158] As a result, an emission current path from the second node N2 to the OLED may be formed by turning on the emission control transistor Tem, the first transistor T1, and the driver transistor Tdr, and current I_OLED may flow into the OLED along the emission current path to enable an emission state.

[0159] Here, the switching transistor Tsw and the second and third transistors T2 and T3 may be in a turn-off state.

[0160] During the emission time T_em, the voltage VN1 applied to the first node N1 may be 'Vdata-Vth', and the voltage VN2 applied to the second node N2 may be 'Vdd'.

[0161] In this case, current I_OLED flowing through the OLED may be defined as in Equation 2:

$$I_{OLED} = 0.5 \cdot K \cdot (V_{dd} - V_{data})^2,$$

wherein k is a proportional constant determined by the structure and physical properties of the structure and physical properties of the driver transistor Tdr, for example, the mobility of the driver transistor Tdr and a ratio W/L of a channel width W of the driver transistor Tdr to

a channel length L thereof.

[0162] As a result, current I_OLED flowing through the OLED during the emission time T_em may be irrespective of the threshold voltage Vth of the driver transistor Tdr and determined by the high-potential voltage Vdd and the data voltage Vdata.

[0163] Accordingly, non-uniformity in luminance caused by differences in the characteristics of transistors may be improved.

[0164] In the pixel structure of the OLED display device according to the first embodiment of the present invention, a high initialization current may flow along the initialization current path and the third current path during the initialization period.

[0165] Also, with application of the high initialization current, voltage division may occur due to on-resistances Ron of the emission control transistor Tem and the third transistor T3, so that the first node N1 cannot be initialized to the reference voltage corresponding to the initialization voltage.

[0166] As a result, the pixel structure of the OLED display device according to the first embodiment of the present invention may be affected by the data voltage Vdata of the previous frame because the first node N1 cannot be initialized to the reference voltage.

[0167] That is, in the pixel structure of the OLED display device according to the first embodiment of the present invention, attainment of luminance may be degraded according to the data voltage Vdata.

[0168] In particular, the pixel structure of the OLED display device according to the first embodiment of the present invention cannot reach white luminance for one frame during a black-to-white conversion, thereby degrading response characteristics.

[0169] However, in the pixel structure of the OLED display device according to the second embodiment of the present invention, since the switching transistor Tsw and the first transistor T1 are turned off during the initialization time T_ini, an initialization current flowing along the initialization current path and the third current path may be reduced.

[0170] Also, since the initialization current is reduced, voltage division due to on-resistances (Ron) of the emission control transistor Tem and the third transistor T3 may be reduced so that the first node N1 can be initialized to about -3.8 V, which is about equal to the reference voltage.

[0171] That is, in the pixel structure of the OLED display device according to the second embodiment of the present invention, control signals of respective transistors may be separated by increasing the number of drivers, so that a time point at which each of the transistors is turned on can be controlled to improve initialization characteristics.

[0172] As a result, the pixel structure of the OLED display device according to the second embodiment of the present invention may be free from the influence of the data voltage Vdata of the previous frame because the

first node N1 may be initialized to the reference voltage.

[0173] Thus, the pixel structure of the OLED display device according to the second embodiment of the present invention may improve degradation of response characteristics, luminance degradation, and degradation of capability of compensating for a deviation in the threshold voltage V_{th} of the driver transistor Tdr.

[0174] FIG. 9 is a schematic equivalent circuit diagram of a pixel region of an OLED display device according to a third embodiment of the present invention, and FIG. 10 is a schematic equivalent circuit diagram of a pixel region of an OLED display device according to a fourth embodiment of the present invention.

[0175] Referring to FIG. 9, a switching transistor Tsw, a driver transistor Tdr, an emission control transistor Tem, first through third transistors T1 to T3, a first capacitor C1, a second capacitor C2, and an OLED may be formed in each of pixel regions.

[0176] In a pixel structure of the OLED display device according to the third embodiment of the present invention, a connection structure among the switching transistor Tsw, the emission control transistor Tem, and the first through third transistors T1 to T3 may be modified.

[0177] Source and gate electrodes of the switching transistor Tsw may be connected to a data line DL and an N+1-th scan line SCL(N+1), respectively, and a drain electrode of the switching transistor Tsw may be connected to a second node N2.

[0178] The switching transistor Tsw may be turned on in response to an N+1-th scan signal applied through the N+1-th scan line SCL(N+1), and apply a data voltage Vdata to the second node N2.

[0179] Source and gate electrodes of the emission control transistor Tem may be connected to a third node N3 and an N+1-th emission control line EL(N+1), respectively, and a drain electrode of the emission control transistor Tem may be connected to one electrode of the OLED.

[0180] The emission control transistor Tem may be turned on in response to an N+1-th emission control signal applied through the N+1-th emission control line EL(N+1), and control an emission time point of the OLED.

[0181] Source and gate electrodes of the first transistor T1 may be connected to a terminal of a high-potential voltage Vdd and an N-th emission control line EL(N), respectively, and a drain electrode of the first transistor T1 may be connected to the second node N2.

[0182] The first transistor T1 may be turned on in response to an N-th emission control signal applied through the N-th emission control line EL(N), and apply the high-potential voltage Vdd to the second node N2. In this case, the high-potential voltage Vdd may be, for example, about 5V.

[0183] Source and gate electrodes of the second transistor T2 may be connected to a third node N3 and an N-th scan line SCL(N), respectively, and a drain electrode of the second transistor T2 may be connected to a first node N1.

[0184] The second transistor T2 may be turned on in response to an N-th scan signal applied through the N-th scan line SCL(N), and apply a reference voltage to the first node N1 to initialize the first node N1.

[0185] Source and gate electrodes of the third transistor T3 may be connected to a drain electrode of the emission control transistor Tem and the N-th scan line SCL(N), respectively, and a drain electrode of the third transistor T3 may be connected to a reference voltage line VL.

[0186] The third transistor T3 may be turned on in response to the N-th scan signal applied through the N-th scan line SCL(N), and apply the reference voltage to an anode electrode of the OLED.

[0187] In the OLED display device according to the third embodiment of the present invention to which the above-described pixel structure is applied, a time point at which each of the transistors is turned on may be controlled using outputs of a scan driver and an emission control driver without forming an additional driver.

[0188] In other words, the OLED display device according to the third embodiment of the present invention may control a time point at which each of the transistors is turned on, using a control signal of the next horizontal line and a control signal of the current horizontal line, thereby improving initialization characteristics.

[0189] Since some components of the OLED display device according to the fourth embodiment are substantially the same as in the third embodiment, differences between the third and fourth embodiments will now be chiefly described.

[0190] As shown in FIG. 10, a switching transistor Tsw, a driver transistor Tdr, an emission control transistor Tem, first through third transistors T1 to T3, a first capacitor C1, a second capacitor C2, and an OLED may be formed in each of pixel regions.

[0191] In a pixel structure of the OLED display device according to the fourth embodiment, a connection structure of the third transistor T3 may be modified.

[0192] Source and gate electrodes of the third transistor T3 may be connected to a drain electrode of the emission control transistor Tem and an N-th scan line SCL(N), respectively, and a drain electrode of the third transistor T3 may be connected to a terminal of a low-potential voltage Vss.

[0193] The third transistor T3 may be turned on in response to an N-th scan signal applied through the N-th scan line SCL(N), and apply a low-potential voltage Vss to an anode electrode of the OLED.

[0194] That is, in the pixel structure of the OLED display device according to the fourth embodiment of the present invention, the drain electrode of the third transistor T3 may be connected to the terminal of the low-potential voltage Vss so that a reference voltage line VL can be eliminated.

[0195] FIG. 11 is a timing diagram of a plurality of control signals applied to the OLED display devices according to the third and fourth embodiments of the present invention. Hereinafter, operations of the pixel regions of

the OLED display devices according to the third and fourth embodiments of the present invention will be described with reference to FIGS. 10 and 11.

[0196] Referring to FIG. 11, during an initialization time T_{ini} , a low-level N-th scan signal $Scan(N)$ and a high-level N+1-th scan signal $Scan(N+1)$ may be applied, and a high-level N-th emission control signal $Em(N)$ and a low-level N+1-th emission control signal $Em(N+1)$ may be applied.

[0197] In this case, the initialization time T_{ini} may be one horizontal period 1H.

[0198] Here, the reference voltage applied through the reference voltage line VL may have a voltage level of, for example, about -4 V, and the low-potential voltage V_{ss} may have a voltage level of, for example, -5 V.

[0199] Accordingly, the second and third transistors T2 and T3 and the emission control transistor T_{em} may be turned on in response to the low-level N-th scan signal $Scan(N)$ and the N+1-th emission control signal $Em(N+1)$, respectively, so the first node N1 may be initialized to the reference voltage.

[0200] That is, in the pixel structures of the OLED display devices according to the third and fourth embodiments of the present invention, since the switching transistor T_{sw} and the first transistor T1 remain turned off during the initialization time T_{ini} , the flow of overcurrent caused by an electrical short between the high-potential voltage V_{dd} and the data voltage V_{data} may be prevented.

[0201] During a sensing time T_{sen} , a low-level N-th scan signal $Scan(N)$ and a low-level N+1-th scan signal $Scan(N+1)$ may be applied, and a high-level N-th emission control signal $Em(N)$ and a high-level N+1-th emission control signal $Em(N+1)$ may be applied.

[0202] In this case, the sensing time T_{sen} may be one horizontal period 1H.

[0203] As a result, the switching transistor T_{sw} and the second and third transistors T2 and T3 may be turned on in response to an N+1-th scan signal $Scan(N+1)$ and a low-level N-th scan signal $Scan(N)$, respectively, and sense the threshold voltage V_{th} of the driver transistor T_{dr} .

[0204] Also, the data voltage V_{data} may be applied to the first node N1 along a sampling/writing current path from the second node N2 to the first node N1, which is formed by turning on the switching transistor T_{sw} and the second transistor T2.

[0205] During the sensing time T_{sen} , the voltage V_{N1} applied to the first node N1 may be ' $V_{data}-V_{th}$ ' or less to enable a normal sampling (or sensing) operation.

[0206] Also, the voltage V_{N2} applied to the second node N2 may be ' V_{data} '.

[0207] During the sensing time T_{sen} , the emission control transistor T_{em} and the first transistor T1 may be in a turn-off state.

[0208] During the holding time T_{hold} , a high-level N-th scan signal $Scan(N)$ may be applied, an N+1-th scan signal $Scan(N+1)$ may be applied during the low-to-high

transition thereof, an N-th emission control signal $Em(N)$ may be applied during the high-to-low transition thereof, and a high-level N+1-th emission control signal $Em(N+1)$ may be applied.

[0209] In this case, the holding time T_{hold} may be two horizontal periods 2H.

[0210] Thus, the N-th scan signal $Scan(N)$ may be applied at a high level during the two horizontal periods 2H, and the N+1-th scan signal $Scan(N+1)$ may be applied at a low level during one horizontal period 1H and applied at a high level during one horizontal period 1H.

[0211] Also, the N-th emission control signal $Em(N)$ may be applied at high level during one horizontal period 1H and applied at a low level during one horizontal period 1H, and the N+1-th emission control signal $Em(N+1)$ may be applied at a high level during two horizontal periods 2H.

[0212] During a first one horizontal period 1H of the holding time T_{hold} , the switching transistor T_{sw} may remain in a turn-on state, the second and third transistors T2 and T3 may be changed from a turn-on state to a turn-off state, and the first transistor T1 and the emission control transistor T_{em} may remain in a turn-off state.

[0213] Thus, since the N-th scan signal $Scan(N)$ applied to one end of the second capacitor C2 makes the low-to-high transition during the first one horizontal period 1H of the holding time T_{hold} , a voltage V_{N1} applied to the first node N1 may rise under the influence of a variation in voltage due to a coupling effect of the second capacitor C2.

[0214] Next, during a second one horizontal period 1H of the holding time T_{hold} , the switching transistor T_{sw} may be changed from a turn-on state to a turn-off state, each of the second and third transistor T2 and T3 and the emission control transistor T_{em} may remain in a turn-off state, and the first transistor T1 may be changed from a turn-off state to a turn-on state.

[0215] Thus, by turning off the switching transistor T_{sw} and turning on the first transistor T1, the second node N2 may be affected by a variation in voltage of the first node N1.

[0216] Accordingly, during the second one horizontal period 1H of the holding time T_{hold} , the voltage V_{N2} applied to the second node N2 may rise and finally reach ' V_{dd} '.

[0217] During an emission time T_{em} , a high-level N-th scan signal $Scan(N)$ and a high-level N+1-th scan signal $Scan(N+1)$ may be applied, and a low-level N-th emission control signal $Em(N)$ and a low-level N+1-th emission control signal $Em(N+1)$ may be applied.

[0218] As a result, by turning on the emission control transistor T_{em} , the first transistor T1, and the driver transistor T_{dr} , an emission current path from the second node N2 to the OLED may be formed, and current I_{OLED} may flow into the OLED along the emission current path to enable an emission state.

[0219] Here, the switching transistor T_{sw} and the second and third transistors T2 and T3 may be in a turn-off

state.

[0220] Meanwhile, as shown in FIG. 11, the N-th scan signal Scan(N) and the N+1-th scan signal Scan(N+1) may be controlled to overlap each other during one horizontal period 1H.

[0221] Also, the N-th emission control signal Em(N) and the N+1-th emission control signal Em(N+1) may be controlled to overlap each other during two horizontal periods 2H.

[0222] As a result, in the OLED display devices according to the third and fourth embodiments of the present invention, a time point at which each of the transistors is turned on may be controlled using the outputs of a scan driver and an emission control driver without forming an additional driver.

[0223] FIGS. 12A and 12B are reference diagrams for explaining initialization characteristics of the OLED display device according to the first embodiment of the present invention, and FIGS. 13A and 13B are reference diagrams for explaining initialization characteristics of the OLED display device according to the second embodiment of the present invention.

[0224] As shown in FIG. 12A, in the pixel structure of the OLED display device according to the first embodiment of the present invention, an initialization current Iref of about 2 μ A is maintained during an initialization time t.

[0225] In this case, the initialization time t may be about 6 μ s.

[0226] As a result, as shown in FIG. 12B, a voltage VN1 applied to the first node N1 during the initialization time t is about -2V, which is higher than an initialization voltage of about -4 V (refer to portion A).

[0227] That is, in the OLED display device according to the first embodiment of the present invention, since a relatively high initialization current Iref flows through an initialization current path during the initialization time t, the first node N1 cannot be initialized to the initialization voltage.

[0228] In contrast, as shown in FIG. 13A, in the pixel structure of the OLED display device according to the second embodiment of the present invention, the initialization current Iref reaches a peak value and sharply drops during the initialization time t.

[0229] As a result, as shown in FIG. 13B, a voltage VN1 applied to the first node N1 during the initialization time t descends and finally reaches an initialization voltage of about -4 V (refer to portion B).

[0230] Accordingly, in the OLED display device according to the second embodiment of the present invention, since a low initialization current Iref flows through an initialization current path during the initialization time t, the first node N1 may be initialized to the initialization voltage.

[0231] Although not shown, the pixel structures of the OLED display devices according to the third and fourth embodiments of the present invention can obtain the same effects as in the second embodiment.

[0232] As explained thus far, in the OLED display devices according to the second through fourth embodiments of the present invention, a time point at which each of transistors is turned on may be controlled without using an additional transistor so that a node connected to a source electrode of a driver transistor can be floated during an initialization time, and a node connected to a gate electrode of the driver transistor can be initialized to an initialization voltage level.

[0233] As a result, degradation of response characteristics, luminance degradation, and degradation of capability of compensating for a deviation in the threshold voltage of the driver transistor can be improved.

[0234] Furthermore, when a touch screen panel is applied to the OLED display devices, touch noise can be improved.

[0235] As described above, in an OLED display device and a method of driving the same according to the present invention, a time point at which each of transistors is turned on may be controlled without using an additional transistor so that a node connected to a source electrode of a driver transistor can be floated during an initialization time, and a node connected to a gate electrode of the driver transistor can be initialized to an initialization voltage level.

[0236] As a result, degradation of response characteristics and luminance degradation can be enhanced, and a threshold voltage of a driver transistor and occurrence of a ripple at a high-potential voltage terminal can be compensated.

[0237] Furthermore, since a high initialization current generated during the initialization time can be reduced and a long initialization time can be applied, a reduction in contrast ratio and a rise in power consumption can be inhibited.

[0238] In addition, when a touch screen panel is applied to an OLED display device according to the present invention, touch noise can be improved.

[0239] It will be apparent to those skilled in the art that various modifications and variations can be made in a display device of the present disclosure without departing from the scope of the invention. Thus, it is intended that the present invention covers the modifications and variations of this invention provided they come within the scope of the appended claims and their equivalents.

Claims

1. An organic light emitting diode (OLED) display device comprising a pixel circuit comprising:

a first transistor (T1), wherein a source electrode of the first transistor (T1) is connected to a high-potential power supply voltage (Vdd) and a drain electrode of the first transistor (T1) is connected to a second node (N2);
a switching transistor, (Tsw) wherein a source

- electrode of the switching transistor (Tsw) is connected to a data line (DL) and a drain electrode of the switching transistor (Tsw) is connected to the second node (N2);
 a second transistor (T2), wherein a source electrode of the second transistor (T2) is connected to a drain electrode of a driver transistor (Tdr) and a drain electrode of the second transistor (T2) is connected to a first node (N1);
 the driver transistor (Tdr) being connected to the second node (N2) and the first node (N1), wherein a source electrode of the driver transistor (Tdr) is connected to the second node (N2) and a gate electrode of the driver transistor (Tdr) is connected to the first node (N1);
 an emission control transistor (Tem), wherein a source electrode of the emission control transistor (Tem) is connected to the drain electrode of the driver transistor (Tdr), and a drain electrode of the emission control transistor (Tem) is connected to one electrode of an OLED;
 a third transistor (T3) connected to the one electrode of the OLED and configured to reduce the voltage on the one electrode of the OLED, wherein a gate electrode of the third transistor (T3) is connected to a gate electrode of the second transistor (T2); and
 a first capacitor (C1) connected between the high-potential power supply voltage (Vdd) terminal and the first node (N1),
 wherein an initialization voltage (V_L , V_{SS}) applied on a drain electrode of the third transistor (T3) is applied to the first node (N1) through the third transistor (T3), the emission control transistor (Tem) and the second transistor (T2) while the second transistor (T2), the third transistor (T3) and the emission control transistor (Tem) are turned on at the same time.
2. The display device of claim 1, wherein a gate electrode of the first transistor (T1) and a gate electrode of the emission control transistor (Tem) are connected to an emission control line (EL), and the first transistor (T1) and the emission control transistor (Tem) are turned on in response to an emission control signal transmitted through the emission control line (EL), and
 wherein a gate electrode of the switching transistor (Tsw) and the gate electrodes of the second and third transistors (T2, T3) are connected to a scan line (SCL), and the switching transistor (Tsw) and the second and third transistors (T2, T3) are turned on in response to a scan signal transmitted through the scan line (SCL).
 3. The display device of claim 1, wherein a gate electrode of the first transistor (T1) is connected to an initialization line (IL) and turned on in response to an initialization signal transmitted through the initialization line (IL),
 a gate electrode of the emission control transistor (Tem) is connected to an emission control line (EL) and turned on in response to an emission control signal transmitted through the emission control line (EL),
 a gate electrode of the switching transistor (Tsw) is connected to a scan line (SCL) and turned on in response to a scan signal transmitted through the scan line (SCL), and
 the gate electrodes of the second and third transistors (T2, T3) are connected to a sensing line (SEL) and turned on in response to a sensing signal transmitted through the sensing line (SEL).
 4. The display device of claim 1, wherein a gate electrode of the first transistor (T1) is connected to an N-th emission control line (EL(N)) and turned on in response to an N-th emission control signal transmitted through the N-th emission control line (EL(N)),
 a gate electrode of the emission control transistor (Tem) is connected to an N+1-th emission control line (EL(N+1)) and turned on in response to an N+1-th emission control signal transmitted through the N+1-th emission control line (EL(N+1)),
 a gate electrode of the switching transistor (Tsw) is connected to an N+1-th scan line (SCL(N+1)) and turned on in response to an N+1-th scan signal transmitted through the N+1-th scan line (SCL(N+1)), and
 the gate electrodes of the second and third transistors (T2, T3) are connected to an N-th scan line (SCL(N)) and turned on in response to an N-th scan signal transmitted through the N-th scan line (SCL(N)).
 5. The display device of claim 4, wherein a drain electrode of the third transistor (T3) is connected to a reference voltage line (VL) configured to supply a reference voltage, or connected to a low-potential voltage terminal configured to supply a low-potential voltage (Vss).
 6. The display device of claim 1, further comprising a second capacitor (C2) connected between the first node (N1) and the gate electrode of the second transistor (T2).
 7. A method of driving an organic light emitting diode (OLED) display device pixel circuit including:
 a first transistor (T1), wherein a source electrode of the first transistor (T1) is connected to a high-potential power supply voltage (Vdd) and a drain electrode of the first transistor (T1) is connected to a second node (N2);
 a switching transistor (Tsw), wherein a source electrode of the switching transistor (Tsw) is

connected to a data line (DL) and a drain electrode of the switching transistor (Tsw) is connected to the second node (N2);
 a second transistor (T2), wherein a source electrode of the second transistor (T2) is connected to a drain electrode of a driver transistor (Tdr) and a drain electrode of the second transistor (T2) is connected to a first node (N1);
 the driver transistor (Tdr) being connected to the second node (N2) and the first node (N1),
 wherein a source electrode of the driver transistor (Tdr) is connected to the second node (N2) and a gate electrode of the driver transistor (Tdr) is connected to the first node (N1);
 an emission control transistor (Tem), wherein a source electrode of the emission control transistor (Tem) is connected to the drain electrode of the driver transistor (Tdr), and a drain electrode of the emission control transistor (Tem) is connected to one electrode of an OLED;
 a third transistor (T3) connected to the one electrode of the OLED and configured to reduce the voltage on the one electrode of the OLED, wherein a gate electrode of the third transistor (T3) is connected to a gate electrode of the second transistor (T2); and
 a first capacitor (C1) connected between the high-potential power supply voltage (Vdd) terminal and the first node (N1), the method comprising:

initializing the first node (N1) to which the gate electrode of the driver transistor (Tdr) is connected such that an initialization voltage (V_L, V_{SS}) applied on a drain electrode of the third transistor (T3) is applied to the first node (N1) through the third transistor (T3), the emission control transistor (Tem) and the second transistor (T2) during turn-on operations of the second and third transistors (T2, T3) and the emission control transistor (Tem);
 sensing a threshold voltage (V_{th}) of the driver transistor (Tdr) by transmitting a data voltage to the first node (N1) during turn-on operations of the switching transistor (Tsw) and the second and third transistors (T2, T3); and
 allowing the OLED to emit light by transmitting the high-potential voltage (Vdd) to the OLED during a turn-on operation of the first transistor (T1) and the emission control transistor (Tem).

8. The method of claim 7, wherein the first transistor (T1) and the emission control transistor (Tem) are turned on in response to an emission control signal transmitted through an emission control line (EL),

and

the switching transistor (Tsw) and the second and third transistors (T2, T3) are turned on in response to a scan signal transmitted through a scan line (SCL).

9. The method of claim 7, wherein the first transistor (T1) is turned on in response to an initialization signal transmitted through an initialization line (IL), the emission control transistor (Tem) is connected to an emission control line (EL) and turned on in response to an emission control signal transmitted through the emission control line (EL), the switching transistor (Tsw) is turned on in response to a scan signal transmitted through a scan line (SCL), and the second and third transistors (T2, T3) are turned on in response to a sensing signal transmitted through a sensing line (SEL).
10. The method of claim 7, wherein the first transistor (T1) is turned on in response to an N-th emission control signal transmitted through an N-th emission control line (EL(N)), the emission control transistor (Tem) is turned on in response to an N+1-th emission control signal transmitted through an N+1-th emission control line (EL(N+1)), the switching transistor (Tsw) is turned on in response to an N+1-th scan signal transmitted through an N+1-th scan line (SCL(N+1)), and the second and third transistors (T2, T3) are turned on in response to an N-th scan signal transmitted through an N-th scan line (SCL(N)).
11. The method of claim 7, wherein the third transistor (T3) applies a reference voltage or a low-potential voltage (V_{ss}) to one electrode of the OLED.

Patentansprüche

1. Anzeigevorrichtung mit organischen Leuchtdioden (OLED), wobei die Anzeigevorrichtung eine Pixelschaltung umfasst, wobei die Pixelschaltung umfasst:

einen ersten Transistor (T1), wobei eine Source-Elektrode des ersten Transistors (T1) mit einer Leistungsversorgungsspannung (Vdd) auf hohem Potential verbunden ist und wobei eine Drain-Elektrode des ersten Transistors (T1) mit einem zweiten Knoten (N2) verbunden ist;
 einen Schalttransistor (Tsw), wobei eine Source-Elektrode des Schalttransistors (Tsw) mit einer Datenleitung (DL) verbunden ist und wobei eine Drain-Elektrode des Schalttransistors (Tsw) mit dem zweiten Knoten (N2) verbunden ist;

- einen zweiten Transistor (T2), wobei eine Source-Elektrode des zweiten Transistors (T2) mit einer Drain-Elektrode eines Treibertransistors (Tdr) verbunden ist und wobei eine Drain-Elektrode des zweiten Transistors (T2) mit einem ersten Knoten (N1) verbunden ist;
 wobei der Treibertransistor (Tdr) mit dem zweiten Knoten (N2) und mit dem ersten Knoten (N1) verbunden ist, wobei eine Source-Elektrode des Treibertransistors (Tdr) mit dem zweiten Knoten (N2) verbunden ist und wobei eine Gate-Elektrode des Treibertransistors (Tdr) mit dem ersten Knoten (N1) verbunden ist;
 einen Emissionssteuerungstransistor (Tem), wobei eine Source-Elektrode des Emissionssteuerungstransistors (Tem) mit der Drain-Elektrode des Treibertransistors (Tdr) verbunden ist und wobei eine Drain-Elektrode des Emissionssteuerungstransistors (Tem) mit einer Elektrode einer OLED verbunden ist;
 einen dritten Transistor (T3), der mit der einen Elektrode der OLED verbunden ist und der dafür konfiguriert ist, die Spannung an der einen Elektrode der OLED zu verringern, wobei eine Gate-Elektrode des dritten Transistors (T3) mit einer Gate-Elektrode des zweiten Transistors (T2) verbunden ist; und
 einen ersten Kondensator (C1), der zwischen den Anschluss der Leistungsversorgungsspannung (Vdd) auf hohem Potential und den ersten Knoten (N1) geschaltet ist,
 wobei eine an eine Drain-Elektrode des dritten Transistors (T3) angelegte Initialisierungsspannung (V_L , V_{SS}) über den dritten Transistor (T3), den Emissionssteuerungstransistor (Tem) und den zweiten Transistor (T2) an den ersten Knoten (N1) angelegt wird, während der zweite Transistor (T2), der dritte Transistor (T3) und der Emissionssteuerungstransistor (Tem) gleichzeitig eingeschaltet werden.
2. Anzeigevorrichtung nach Anspruch 1, wobei eine Gate-Elektrode des ersten Transistors (T1) und eine Gate-Elektrode des Emissionssteuerungstransistors (Tem) mit einer Emissionssteuerungsleitung (EL) verbunden sind und wobei der erste Transistor (T1) und der Emissionssteuerungstransistor (Tem) als Reaktion auf ein über die Emissionssteuerungsleitung (EL) übertragenes Emissionssteuerungssignal eingeschaltet werden, und
 wobei eine Gate-Elektrode des Schalttransistors (Tsw) und die Gate-Elektroden des zweiten und des dritten Transistors (T2, T3) mit einer Abtastleitung (SCL) verbunden sind, und wobei der Schalttransistor (Tsw) und der zweite und der dritte Transistor (T2, T3) als Reaktion auf ein über die Abtastleitung (SCL) übertragenes Abtastsignal eingeschaltet werden.
3. Anzeigevorrichtung nach Anspruch 1, wobei eine Gate-Elektrode des ersten Transistors (T1) mit einer Initialisierungsleitung (IL) verbunden ist und als Reaktion auf ein über die Initialisierungsleitung (IL) übertragenes Initialisierungssignal eingeschaltet wird,
 eine Gate-Elektrode des Emissionssteuerungstransistors (Tem) mit einer Emissionssteuerungsleitung (EL) verbunden ist und als Reaktion auf ein über die Emissionssteuerungsleitung (EL) übertragenes Emissionssteuerungssignal eingeschaltet wird,
 eine Gate-Elektrode des Schalttransistors (Tsw) mit einer Abtastleitung (SCL) verbunden ist und als Reaktion auf ein über die Abtastleitung (SCL) übertragenes Abtastsignal eingeschaltet wird, und
 die Gate-Elektroden des zweiten und des dritten Transistors (T2, T3) mit einer Erfassungsleitung (SEL) verbunden sind und als Reaktion auf ein über die Erfassungsleitung (SEL) übertragenes Erfassungssignal eingeschaltet werden.
4. Anzeigevorrichtung nach Anspruch 1, wobei eine Gate-Elektrode des ersten Transistors (T1) mit einer N-ten Emissionssteuerungsleitung (EL(N)) verbunden ist und als Reaktion auf ein über die N-te Emissionssteuerungsleitung (EL(N)) übertragenes N-tes Emissionssteuerungssignal eingeschaltet wird,
 eine Gate-Elektrode des Emissionssteuerungstransistors (Tem) mit einer N+1-ten Emissionssteuerungsleitung (EL(N+1)) verbunden ist und als Reaktion auf ein über die N+1-te Emissionssteuerungsleitung (EL(N+1)) übertragenes N+1-tes Emissionssteuerungssignal eingeschaltet wird,
 eine Gate-Elektrode des Schalttransistors (Tsw) mit einer N+1-ten Abtastleitung (SCL(N+1)) verbunden ist und als Reaktion auf ein über die N+1-te Abtastleitung (SCL(N+1)) übertragenes N+1-tes Abtastsignal eingeschaltet wird, und
 die Gate-Elektroden des zweiten und des dritten Transistors (T2, T3) mit einer N-ten Abtastleitung (SCL(N)) verbunden sind und als Reaktion auf ein über die N-te Abtastleitung (SCL(N)) übertragenes N-tes Abtastsignal eingeschaltet werden.
5. Anzeigevorrichtung nach Anspruch 4, wobei eine Drain-Elektrode des dritten Transistors (T3) mit einer Referenzspannungsleitung (VL) verbunden ist, die dafür konfiguriert ist, eine Referenzspannung zuzuführen, oder mit einem Anschluss einer Spannung auf tiefem Potential verbunden ist, der dafür konfiguriert ist, eine Spannung (Vss) auf tiefem Potential zuzuführen.
6. Anzeigevorrichtung nach Anspruch 1, die ferner einen zweiten Kondensator (C2) umfasst, der zwischen den ersten Knoten (N1) und die Gate-Elektrode des zweiten Transistors (T2) geschaltet ist.

7. Verfahren zum Ansteuern einer Pixelschaltung einer Anzeigevorrichtung mit organischen Leuchtdioden (OLED), wobei die Pixelschaltung enthält:

einen ersten Transistor (T1), wobei eine Source-Elektrode des ersten Transistors (T1) mit einer Leistungsversorgungsspannung (Vdd) auf hohem Potential verbunden ist und wobei eine Drain-Elektrode des ersten Transistors (T1) mit einem zweiten Knoten (N2) verbunden ist;
 einen Schalttransistor (Tsw), wobei eine Source-Elektrode des Schalttransistors (Tsw) mit einer Datenleitung (DL) verbunden ist und wobei eine Drain-Elektrode des Schalttransistors (Tsw) mit dem zweiten Knoten (N2) verbunden ist;
 einen zweiten Transistor (T2), wobei eine Source-Elektrode des zweiten Transistors (T2) mit einer Drain-Elektrode eines Treibertransistors (Tdr) verbunden ist und wobei eine Drain-Elektrode des zweiten Transistors (T2) mit einem ersten Knoten (N1) verbunden ist;
 wobei der Treibertransistor (Tdr) mit dem zweiten Knoten (N2) und mit dem ersten Knoten (N1) verbunden ist, wobei eine Source-Elektrode des Treibertransistors (Tdr) mit dem zweiten Knoten (N2) verbunden ist und wobei eine Gate-Elektrode des Treibertransistors (Tdr) mit dem ersten Knoten (N1) verbunden ist;
 einen Emissionssteuerungstransistor (Tem), wobei eine Source-Elektrode des Emissionssteuerungstransistors (Tem) mit der Drain-Elektrode des Treibertransistors (Tdr) verbunden ist und wobei eine Drain-Elektrode des Emissionssteuerungstransistors (Tem) mit einer Elektrode einer OLED verbunden ist;
 einen dritten Transistor (T3), der mit der einen Elektrode der OLED verbunden ist und der dafür konfiguriert ist, die Spannung an der einen Elektrode der OLED zu verringern, wobei eine Gate-Elektrode des dritten Transistors (T3) mit einer Gate-Elektrode des zweiten Transistors (T2) verbunden ist; und
 einen ersten Kondensator (C1), der zwischen dem Anschluss der Leistungsversorgungsspannung (Vdd) auf hohem Potential und dem ersten Knoten (N1) geschaltet ist, wobei das Verfahren umfasst:

Initialisieren des ersten Knotens (N1), mit dem die Gate-Elektrode des Treibertransistors (Tdr) verbunden ist, in der Weise, dass eine an eine Drain-Elektrode des dritten Transistors (T3) angelegte Initialisierungsspannung (V_L , V_{SS}) während Einschaltoperationen des zweiten und des dritten Transistors (T2, T3) und des Emissionssteuerungstransistors (Tem) über den dritten

Transistor (T3), den Emissionssteuerungstransistor (Tem) und den zweiten Transistor (T2) an den ersten Knoten (N1) angelegt wird;

Erfassen einer Schwellenspannung (V_{th}) des Treibertransistors (Tdr) durch Übertragen einer Datenspannung an den ersten Knoten (N1) während Einschaltoperationen des Schalttransistors (Tsw) und des zweiten und des dritten Transistors (T2, T3); und Ermöglichen, dass die OLED Licht emittiert, durch Übertragen der Spannung (Vdd) auf hohem Potential an die OLED während einer Einschaltoperation des ersten Transistors (T1) und des Emissionssteuerungstransistors (Tem).

8. Verfahren nach Anspruch 7, wobei der erste Transistor (T1) und der Emissionssteuerungstransistor (Tem) als Reaktion auf ein über eine Emissionssteuerungsleitung (EL) übertragenes Emissionssteuerungssignal eingeschaltet werden, und der Schalttransistor (Tsw) und der zweite und der dritte Transistor (T2, T3) als Reaktion auf ein über eine Abtastleitung (SCL) übertragenes Abtastsignal eingeschaltet werden.
9. Verfahren nach Anspruch 7, wobei der erste Transistor (T1) als Reaktion auf ein über eine Initialisierungsleitung (IL) übertragenes Initialisierungssignal eingeschaltet wird, der Emissionssteuerungstransistor (Tem) als Reaktion auf ein über die Emissionssteuerungsleitung (EL) übertragenes Emissionssteuerungssignal mit einer Emissionssteuerungsleitung (EL) verbunden und eingeschaltet wird, der Schalttransistor (Tsw) als Reaktion auf ein über eine Abtastleitung (SCL) übertragenes Abtastsignal eingeschaltet wird und der zweite und der dritte Transistor (T2, T3) als Reaktion auf ein über eine Erfassungsleitung (SEL) übertragenes Erfassungssignal eingeschaltet werden.
10. Verfahren nach Anspruch 7, wobei der erste Transistor (T1) als Reaktion auf ein über eine N-te Emissionssteuerungsleitung (EL(N)) übertragenes N-tes Emissionssteuerungssignal eingeschaltet wird, der Emissionssteuerungstransistor (Tem) als Reaktion auf ein über eine N+1-te Emissionssteuerungsleitung (EL(N+1)) übertragenes N+1-tes Emissionssteuerungssignal eingeschaltet wird, der Schalttransistor (Tsw) als Reaktion auf ein über eine N+1-te Abtastleitung (SCL(N+1)) übertragenes N+1-tes Abtastsignal eingeschaltet wird, und der zweite und der dritte Transistor (T2, T3) als Reaktion auf ein über eine N-te Abtastleitung (SCL(N)) übertragenes N-tes Abtastsignal eingeschaltet werden.

11. Verfahren nach Anspruch 7, wobei der dritte Transistor (T3) an eine Elektrode der OLED eine Referenzspannung oder eine Spannung (Vss) auf tiefem Potential anlegt.

Revendications

1. Dispositif d'affichage à diodes électroluminescentes organiques (OLED) comprenant un circuit de pixels comprenant :

un premier transistor (T1), dans lequel une électrode de source du premier transistor (T1) est reliée à une tension d'alimentation électrique à haut potentiel (Vdd) et une électrode de drain du premier transistor (T1) est reliée à un deuxième noeud (N2) ;

un transistor de commutation (Tsw), dans lequel une électrode de source du transistor de commutation (Tsw) est reliée à une ligne de données (DL) et une électrode de drain du transistor de commutation (Tsw) est reliée au deuxième noeud (N2) ;

un deuxième transistor (T2), dans lequel une électrode de source du deuxième transistor (T2) est reliée à une électrode de drain d'un transistor d'attaque (Tdr) et

une électrode de drain du deuxième transistor (T2) est reliée à un premier noeud (N1) ;

le transistor d'attaque (Tdr) étant relié au deuxième noeud (N2) et au premier noeud (N1),

dans lequel une électrode de source du transistor d'attaque (Tdr) est reliée au deuxième noeud (N2) et une électrode de grille du transistor d'attaque (Tdr) est reliée au premier noeud (N1) ;

un transistor de régulation d'émission (Tem), dans lequel une électrode de source du transistor de régulation d'émission (Tem) est reliée à l'électrode de drain du transistor d'attaque (Tdr), et une électrode de drain du transistor de régulation d'émission (Tem) est reliée à une électrode d'une OLED ;

un troisième transistor (T3) relié à une électrode de l'OLED et configuré pour réduire la tension sur l'électrode de l'OLED, dans lequel une électrode de grille du troisième transistor (T3) est reliée à une électrode de grille du deuxième transistor (T2) ; et

un premier condensateur (C1) relié entre la borne de tension d'alimentation électrique à haut potentiel (Vdd) et le premier noeud (N1), dans lequel une tension d'initialisation (V_L , V_{SS}) appliquée à une électrode de drain du troisième transistor (T3) est appliquée au premier noeud (N1) par l'intermédiaire du troisième transistor (T3), du transistor de régulation d'émission (Tem) et du deuxième transistor (T2) pendant

que le deuxième transistor (T2), le troisième transistor (T3) et le transistor de régulation d'émission (Tem) sont mis sous tension en même temps.

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2. Dispositif d'affichage selon la revendication 1, dans lequel une électrode de grille du premier transistor (T1) et une électrode de grille du transistor de régulation d'émission (Tem) sont reliées à une ligne de régulation d'émission (EL), et le premier transistor (T1) et le transistor de régulation d'émission (Tem) sont mis sous tension en réponse à un signal de régulation d'émission transmis par l'intermédiaire de la ligne de régulation d'émission (EL), et dans lequel une électrode de grille du transistor de commutation (Tsw) et les électrodes de grille des deuxième et troisième transistors (T2, T3) sont reliées à une ligne de balayage (SCL), et le transistor de commutation (Tsw) et les deuxième et troisième transistors (T2, T3) sont mis sous tension en réponse à un signal de balayage transmis par l'intermédiaire de la ligne de balayage (SCL).

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3. Dispositif d'affichage selon la revendication 1, dans lequel une électrode de grille du premier transistor (T1) est reliée à une ligne d'initialisation (IL) et mise sous tension en réponse à un signal d'initialisation transmis par l'intermédiaire de la ligne d'initialisation (IL),

une électrode de grille du transistor de régulation d'émission (Tem) est reliée à une ligne de régulation d'émission (EL) et mise sous tension en réponse à un signal de régulation d'émission transmis par l'intermédiaire de la ligne de régulation d'émission (EL), une électrode de grille du transistor de commutation (Tsw) est reliée à une ligne de balayage (SCL) et mise sous tension en réponse à un signal de balayage transmis par l'intermédiaire de la ligne de balayage (SCL), et

les électrodes de grille des deuxième et troisième transistors (T2, T3) sont reliées à une ligne de détection (SEL) et mises sous tension en réponse à un signal de détection transmis par l'intermédiaire de la ligne de détection (SEL).

4. Dispositif d'affichage selon la revendication 1, dans lequel une électrode de grille du premier transistor (T1) est reliée à une $N^{\text{ième}}$ ligne de régulation d'émission (EL(N)) et mise sous tension en réponse à un $N^{\text{ième}}$ signal de régulation d'émission transmis par l'intermédiaire de la $N^{\text{ième}}$ ligne de régulation d'émission (EL(N)),

une électrode de grille du transistor de régulation d'émission (Tem) est reliée à une $N+1^{\text{ième}}$ ligne de régulation d'émission (EL(N+1)) et mise sous tension en réponse à un $N+1^{\text{ième}}$ signal de régulation d'émission transmis par l'intermédiaire de la $N+1^{\text{ième}}$ ligne de régulation d'émission (EL(N+1)),

une électrode de grille du transistor de commutation (Tsw) est reliée à une N+1^{ième} ligne de balayage (SCL(N+1)) et mise sous tension en réponse à un N+1^{ième} signal de balayage transmis par l'intermédiaire de la N+1^{ième} ligne de balayage (SCL(N+1)), et les électrodes de grille des deuxième et troisième transistors (T2, T3) sont reliées à une N^{ième} ligne de balayage (SCL(N)) et mises sous tension en réponse à un N^{ième} signal de balayage transmis par l'intermédiaire de la N^{ième} ligne de balayage (SCL(N)).

5. Dispositif d'affichage selon la revendication 4, dans lequel une électrode de drain du troisième transistor (T3) est reliée à une ligne de tension de référence (VL) configurée pour fournir une tension de référence, ou reliée à une borne de tension à bas potentiel configurée pour fournir une tension à bas potentiel (Vss).
6. Dispositif d'affichage selon la revendication 1, comprenant en outre un deuxième condensateur (C2) relié entre le premier noeud (N1) et l'électrode de grille du deuxième transistor (T2).
7. Procédé d'attaque d'un circuit de pixels de dispositif d'affichage à diodes électroluminescentes organiques (OLED) comprenant :

un premier transistor (T1), dans lequel une électrode de source du premier transistor (T1) est reliée à une tension d'alimentation électrique à haut potentiel (Vdd) et une électrode de drain du premier transistor (T1) est reliée à un deuxième noeud (N2) ;
 un transistor de commutation (Tsw), dans lequel une électrode de source du transistor de commutation (Tsw) est reliée à une ligne de données (DL) et une électrode de drain du transistor de commutation (Tsw) est reliée au deuxième noeud (N2) ;
 un deuxième transistor (T2), dans lequel une électrode de source du deuxième transistor (T2) est reliée à une électrode de drain d'un transistor d'attaque (Tdr) et une électrode de drain du deuxième transistor (T2) est reliée à un premier noeud (N1) ;
 le transistor d'attaque (Tdr) étant relié au deuxième noeud (N2) et au premier noeud (N1), dans lequel une électrode de source du transistor d'attaque (Tdr) est reliée au deuxième noeud (N2) et une électrode de grille du transistor d'attaque (Tdr) est reliée au premier noeud (N1) ;
 un transistor de régulation d'émission (Tem), dans lequel une électrode de source du transistor de régulation d'émission (Tem) est reliée à l'électrode de drain du transistor d'attaque (Tdr), et une électrode de drain du transistor de régulation d'émission (Tem) est reliée à une électro-

de d'une OLED ;
 un troisième transistor (T3) relié à une électrode de l'OLED et configuré pour réduire la tension sur l'électrode de l'OLED, dans lequel une électrode de grille du troisième transistor (T3) est reliée à une électrode de grille du deuxième transistor (T2) ; et
 un premier condensateur (C1) relié entre la borne de tension d'alimentation électrique à haut potentiel (Vdd) et le premier noeud (N1), le procédé comprenant :

l'initialisation du premier noeud (N1) auquel l'électrode de grille du transistor d'attaque (Tdr) est reliée de sorte qu'une tension d'initialisation (V_L , V_{SS}) appliquée à une électrode de drain du troisième transistor (T3) soit appliquée au premier noeud (N1) par l'intermédiaire du troisième transistor (T3), du transistor de régulation d'émission (Tem) et du deuxième transistor (T2) pendant des opérations de mise sous tension des deuxième et troisième transistors (T2, T3) et du transistor de régulation d'émission (Tem) ;
 la détection d'une tension de seuil (V_{th}) du transistor d'attaque (Tdr) par la transmission d'une tension de données au premier noeud (N1) au cours d'opérations de mise sous tension du transistor de commutation (Tsw) et des deuxième et troisième transistors (T2, T3) ; et
 l'autorisation à l'OLED d'émettre une lumière par la transmission de la tension à haut potentiel (Vdd) à l'OLED au cours d'une opération de mise sous tension du premier transistor (T1) et du transistor de régulation d'émission (Tem).

8. Procédé selon la revendication 7, dans lequel le premier transistor (T1) et le transistor de régulation d'émission (Tem) sont mis sous tension en réponse à un signal de régulation d'émission transmis par l'intermédiaire d'une ligne de régulation d'émission (EL), et le transistor de commutation (Tsw) et les deuxième et troisième transistors (T2, T3) sont mis sous tension en réponse à un signal de balayage transmis par l'intermédiaire d'une ligne de balayage (SCL).
9. Procédé selon la revendication 7, dans lequel le premier transistor (T1) est mis sous tension en réponse à un signal d'initialisation transmis par l'intermédiaire d'une ligne d'initialisation (IL), le transistor de régulation d'émission (Tem) est relié à une ligne de régulation d'émission (EL) et mis sous tension en réponse à un signal de régulation d'émission transmis par l'intermédiaire de la ligne de régulation d'émission (EL).

sion (EL), le transistor de commutation (Tsw) est mis sous tension en réponse à un signal de balayage transmis par l'intermédiaire d'une ligne de balayage (SCL), et les deuxième et troisième transistors (T2, T3) sont mis sous tension en réponse à un signal de détection transmis par l'intermédiaire d'une ligne de détection (SEL). 5

10. Procédé selon la revendication 7, dans lequel le premier transistor (T1) est mis sous tension en réponse à un N^{ième} signal de régulation d'émission transmis par l'intermédiaire d'une N^{ième} ligne de régulation d'émission (EL(N)), 10
- le transistor de régulation d'émission (Tem) est mis sous tension en réponse à un N+1^{ième} signal de régulation d'émission transmis par l'intermédiaire d'une N+1^{ième} ligne de régulation d'émission (EL(N+1)), 15
- le transistor de commutation (Tsw) est mis sous tension en réponse à un N+1^{ième} signal de balayage transmis par l'intermédiaire d'une N+1^{ième} ligne de balayage (SCL(N+1)), et 20
- les deuxième et troisième transistors (T2, T3) sont mis sous tension en réponse à un N^{ième} signal de balayage transmis par l'intermédiaire d'une N^{ième} ligne de balayage (SCL(N)). 25
11. Procédé selon la revendication 7, dans lequel le troisième transistor (T3) applique une tension de référence ou une tension à bas potentiel (Vss) à une électrode de l'OLED. 30

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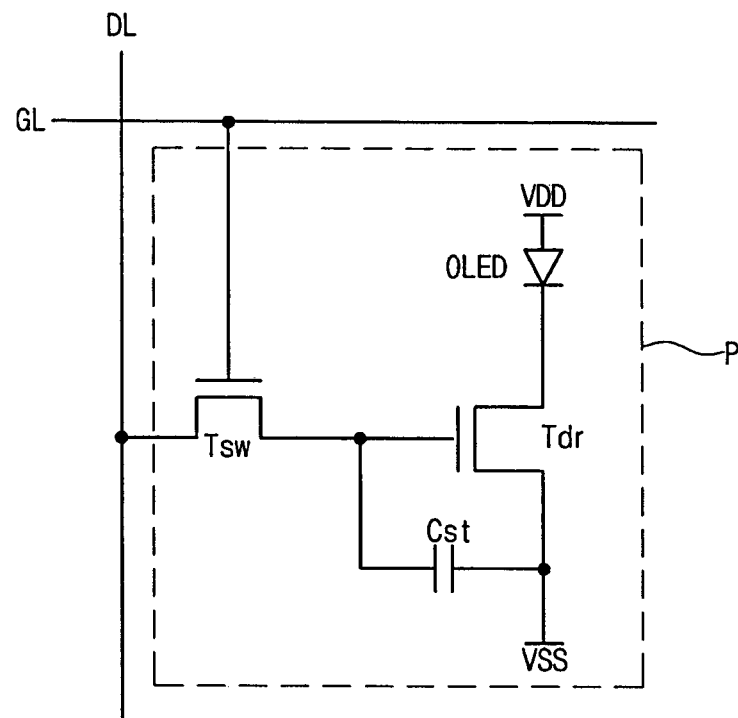


FIG 1

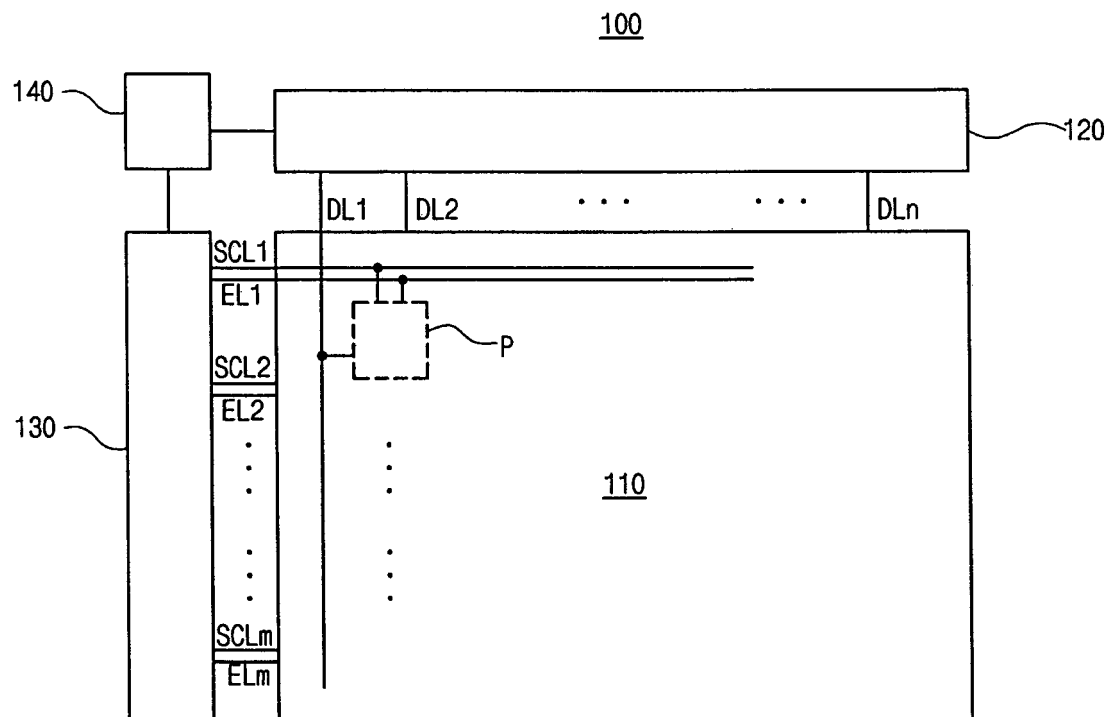


FIG 2

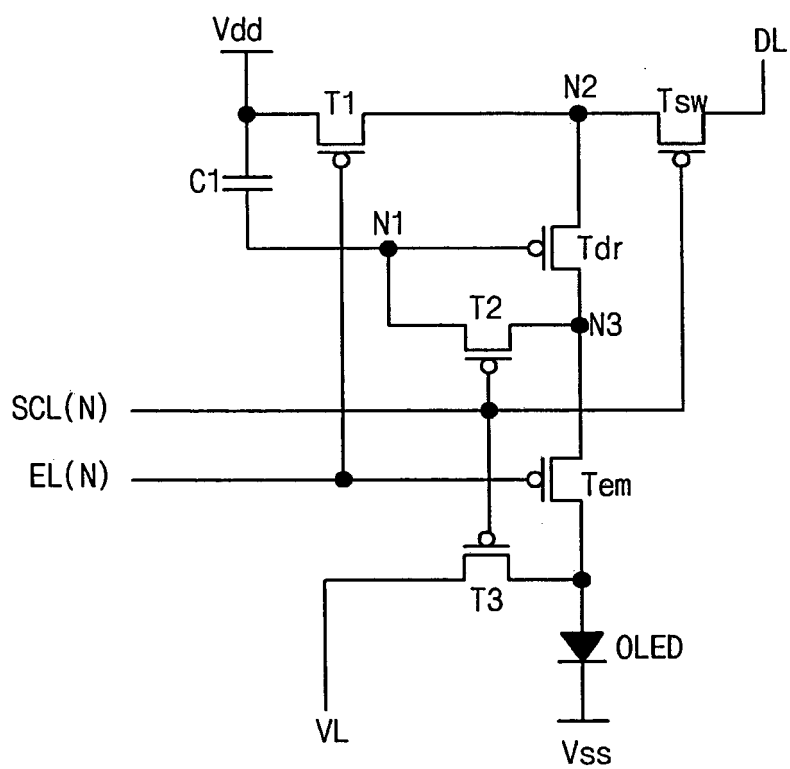


FIG 3

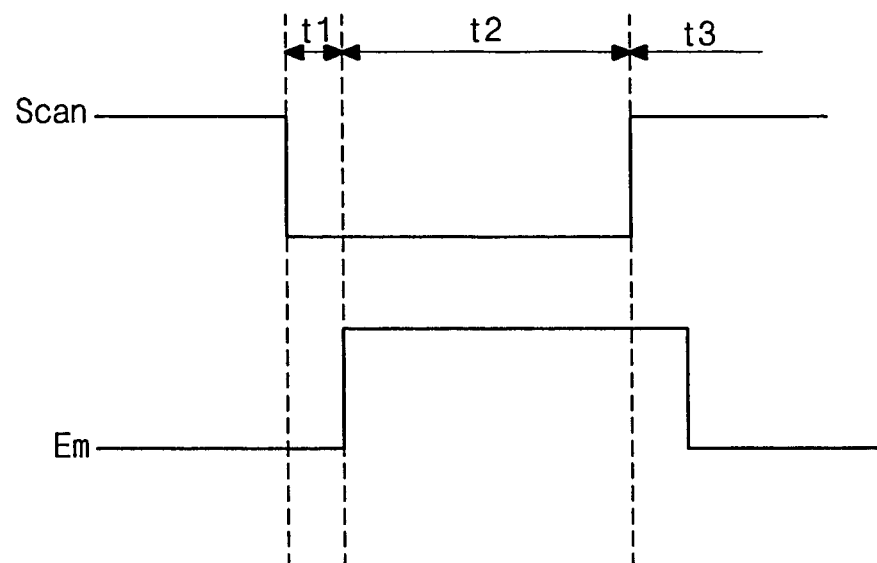


FIG 4

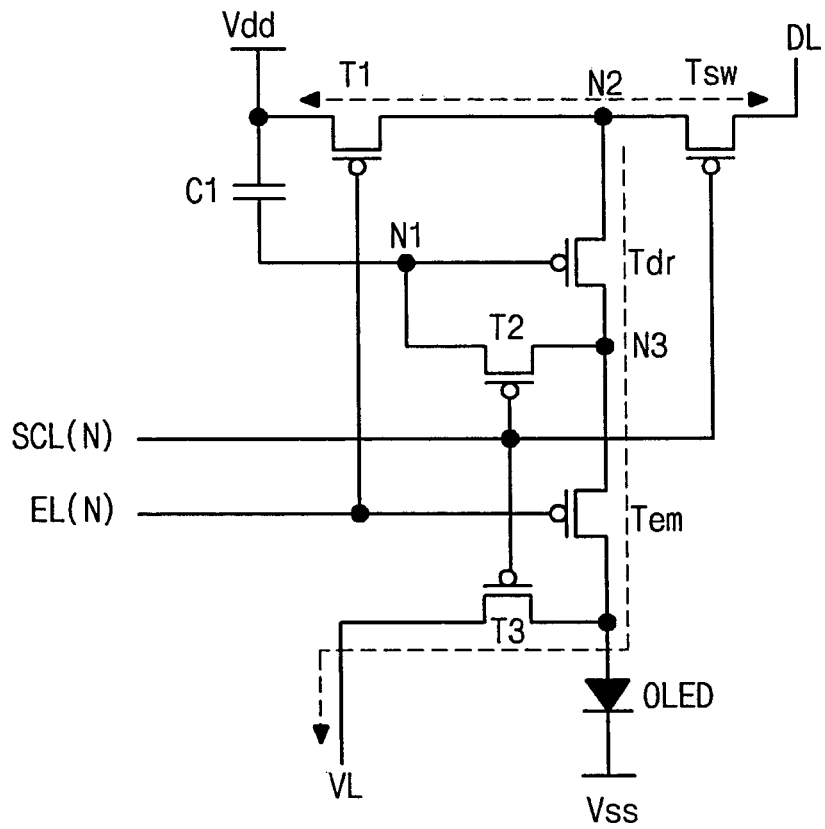


FIG. 5

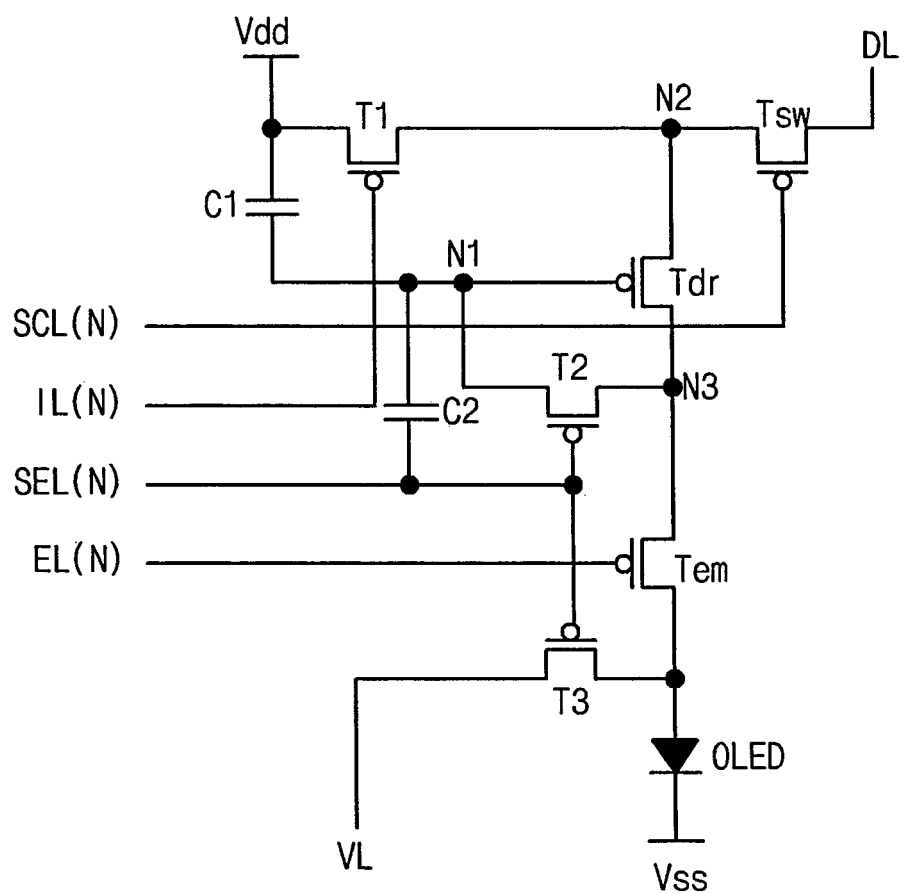


FIG. 6

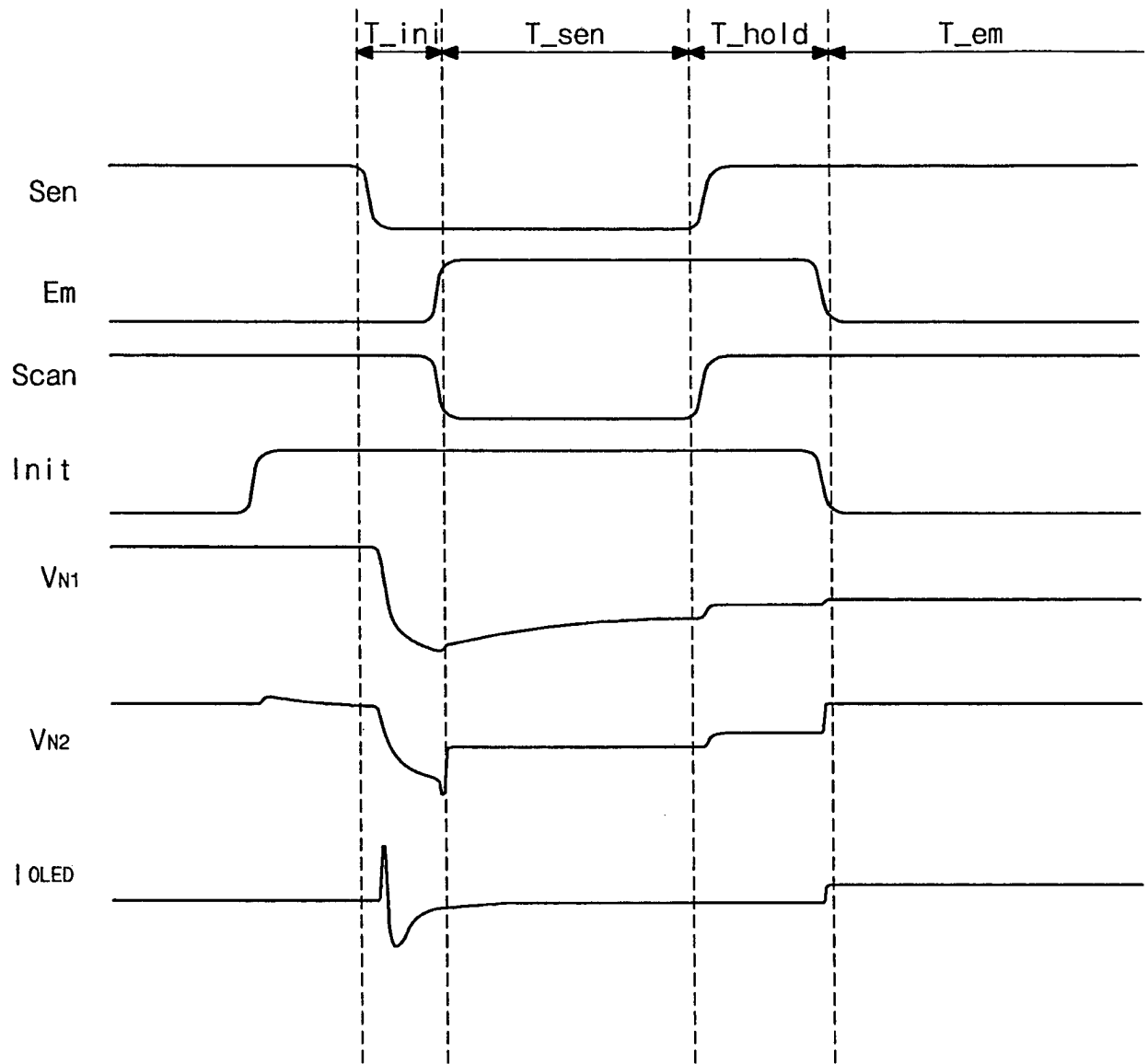


FIG 7

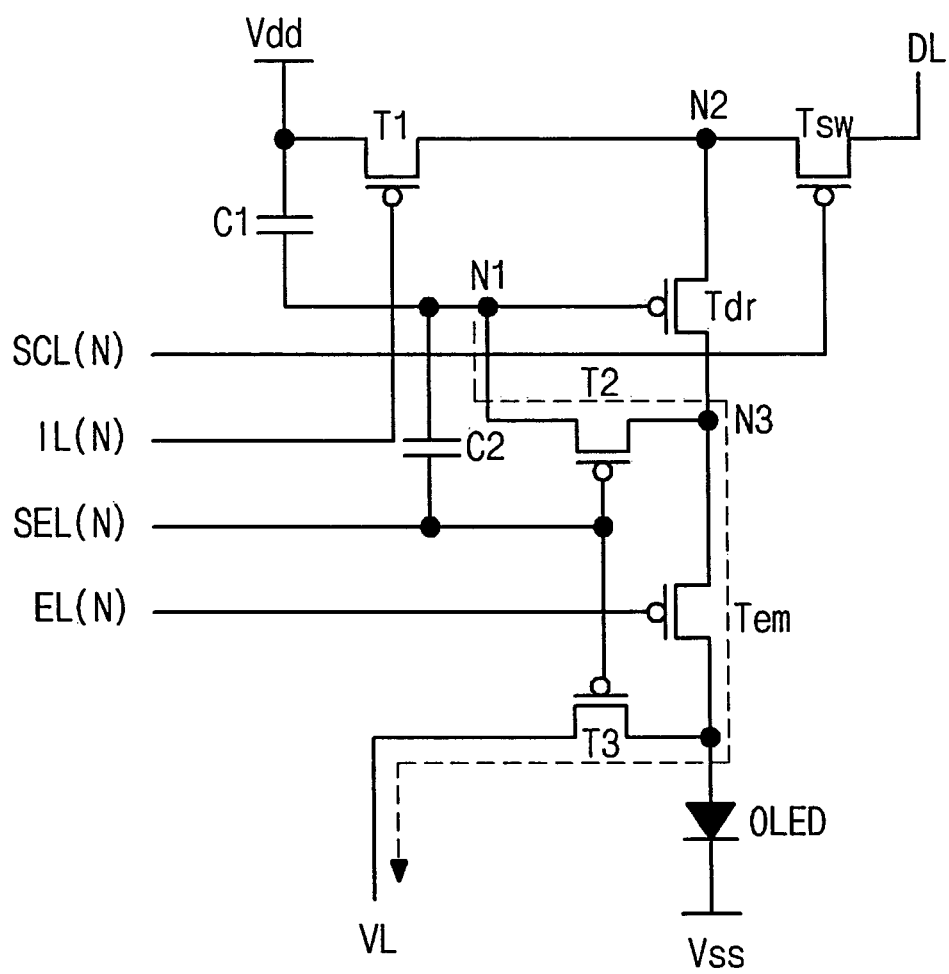


FIG 8

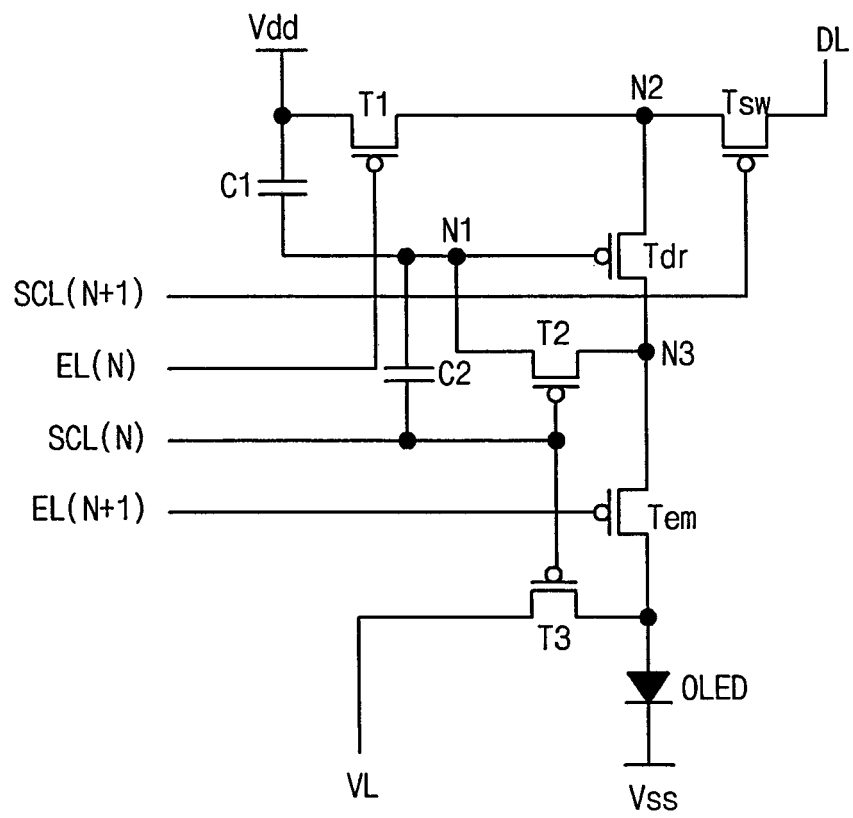
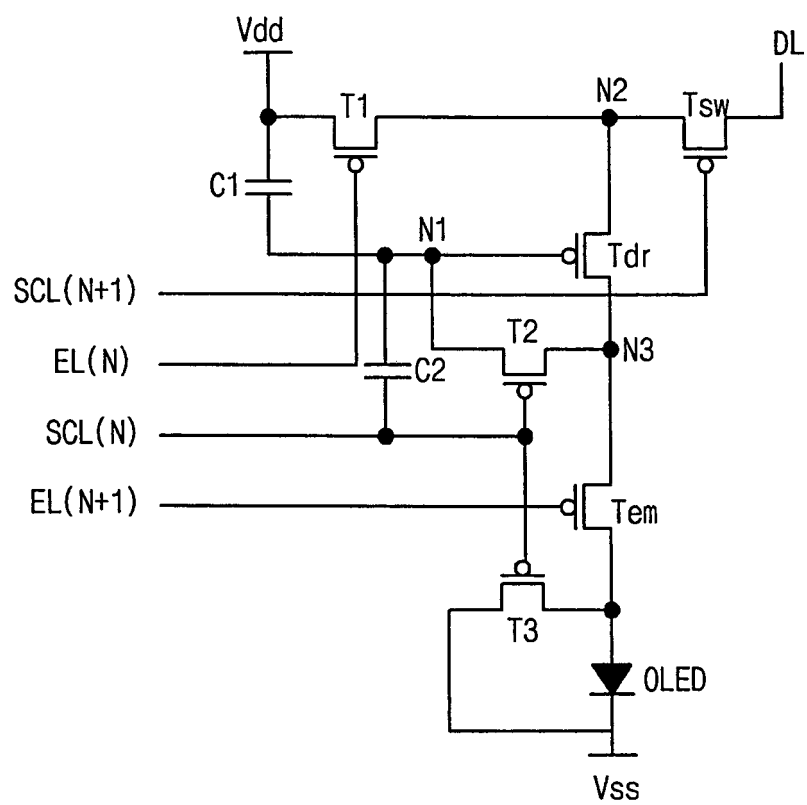
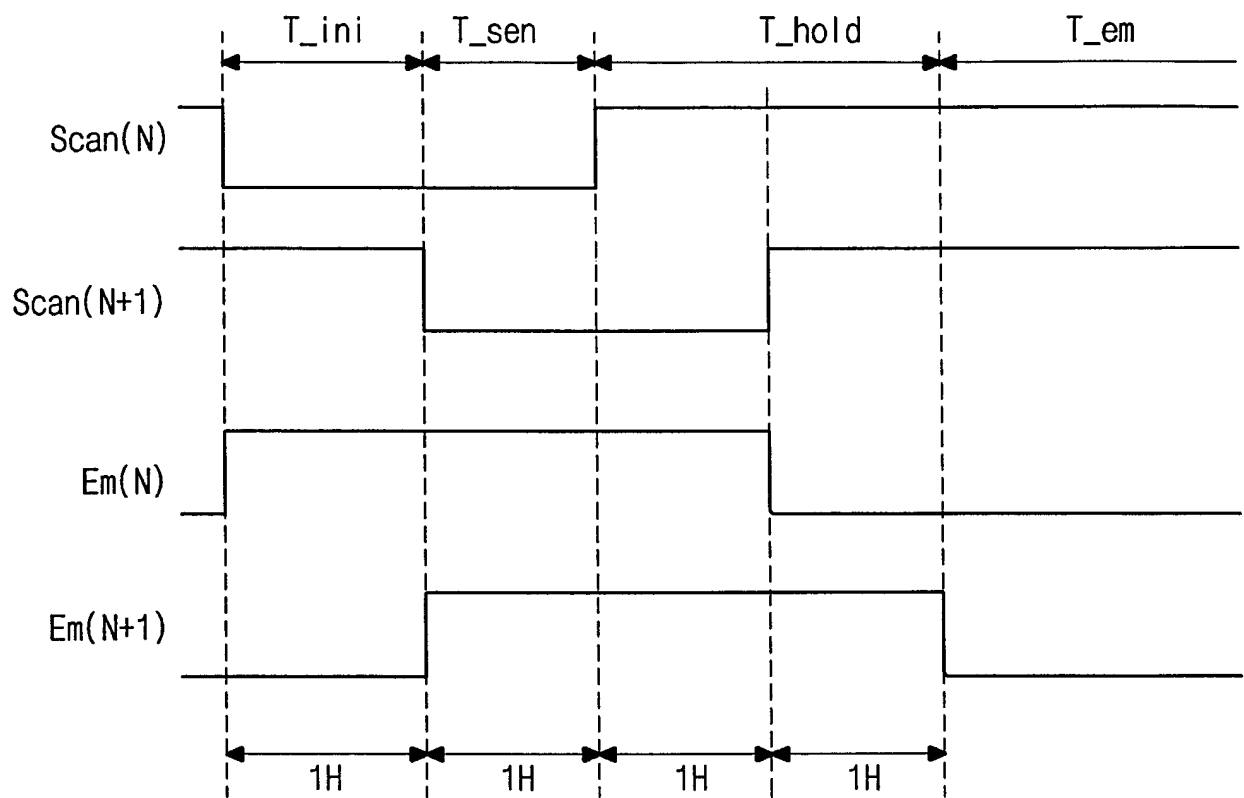


FIG. 9

**FIG 10**

**FIG 11**

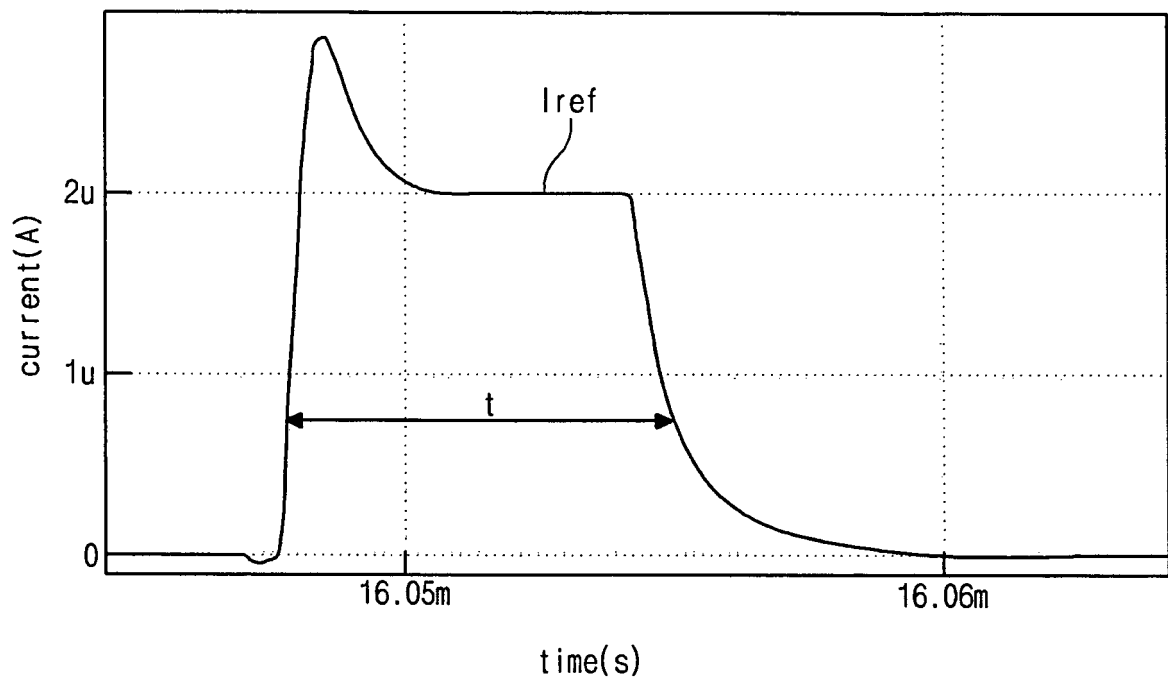


FIG. 12A

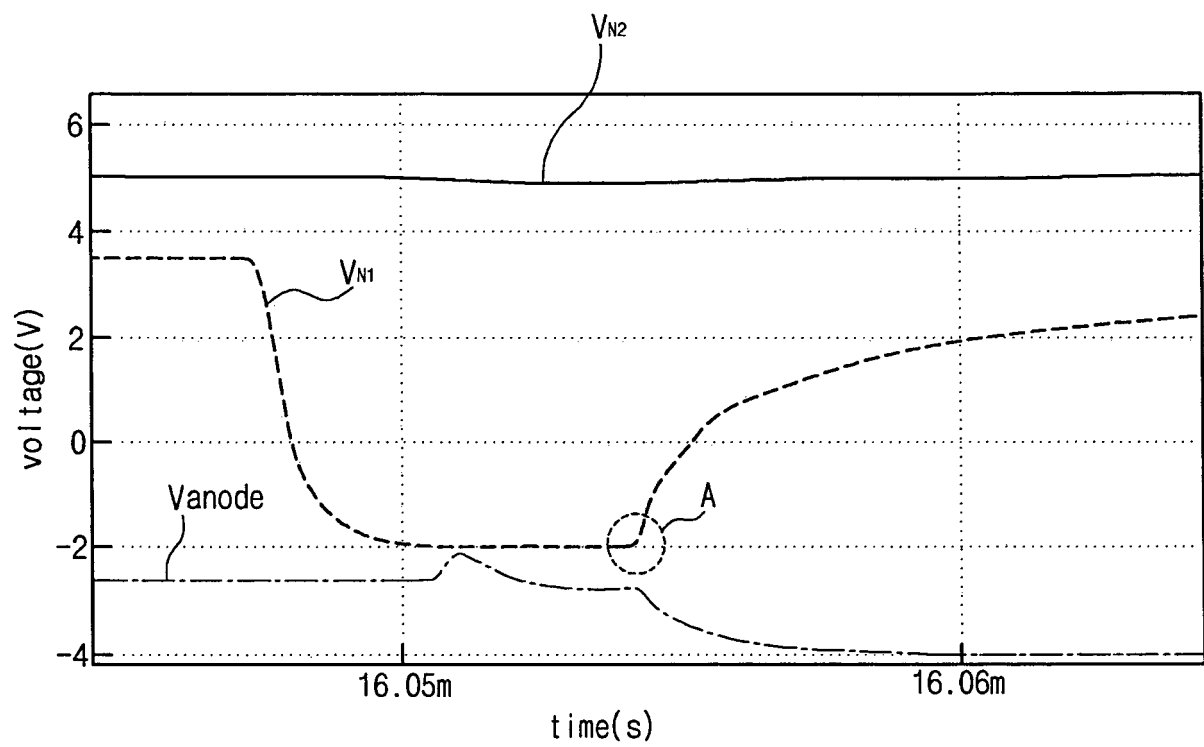


FIG. 12B

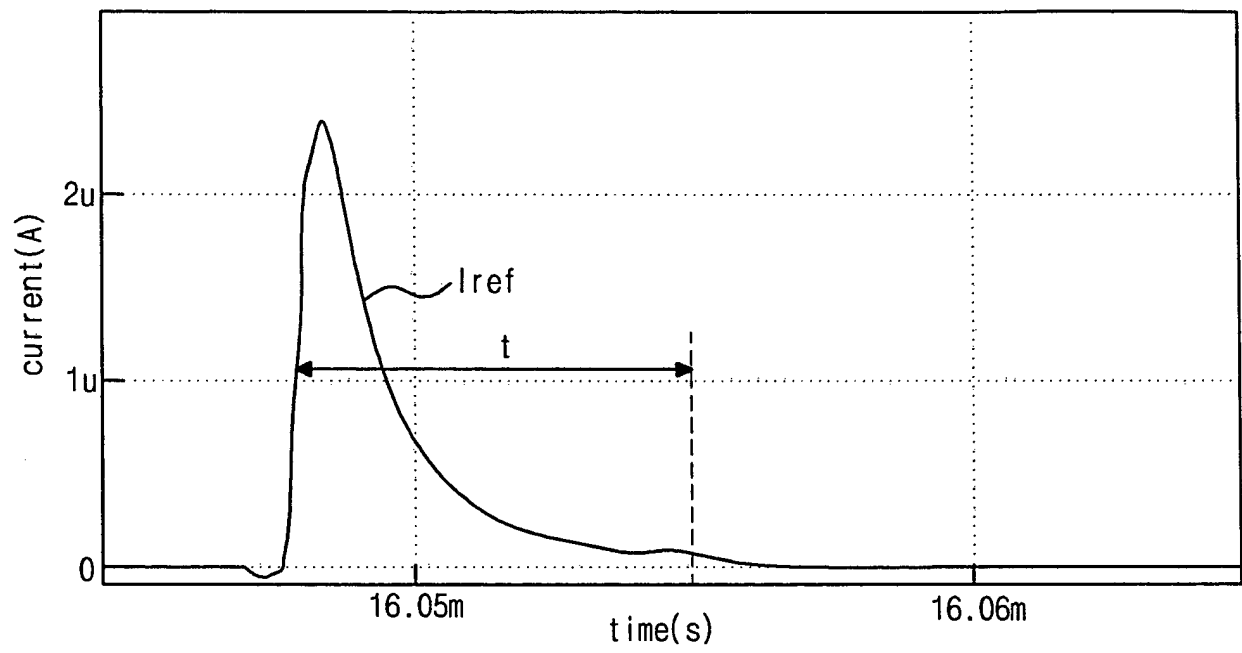
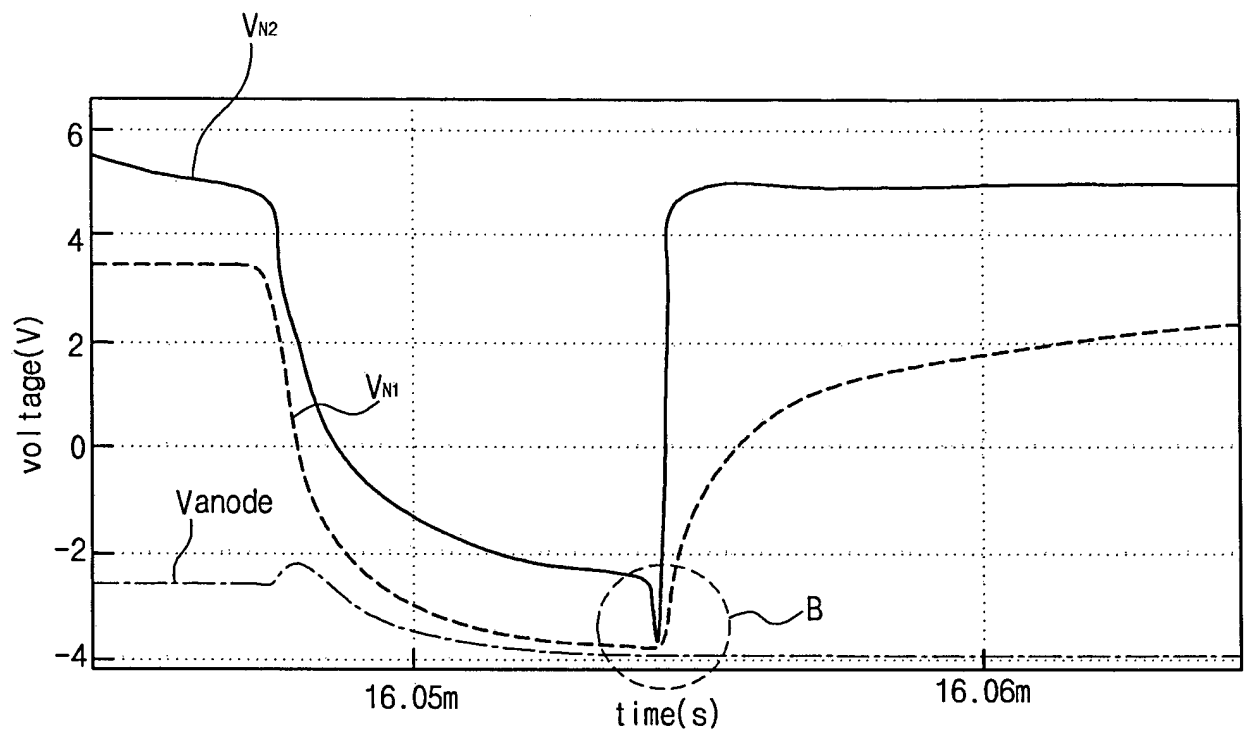


FIG 13A

**FIG 13B**

REFERENCES CITED IN THE DESCRIPTION

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- US 20100164847 A1 [0024]
- US 20080150846 A1 [0025]

专利名称(译)	有机发光二极管显示装置及其驱动方法		
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申请号	EP2012007782	申请日	2012-11-16
[标]申请(专利权)人(译)	乐金显示有限公司		
申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
[标]发明人	LEE JUNG MIN SIM JAE HO		
发明人	LEE, JUNG-MIN SIM, JAE-HO		
IPC分类号	G09G3/32		
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优先权	1020110128917 2011-12-05 KR		
其他公开文献	EP2602783A1		
外部链接	Espacenet		

摘要(译)

提供一种有机发光二极管 (OLED) 显示装置及其驱动方法。在不使用附加晶体管的情况下控制每个晶体管导通的时间点，使得连接到驱动晶体管 (Tdr) 的源电极的节点 (N2) 可以浮置，并且节点 (N1) 连接到可以将驱动晶体管 (Tdr) 的栅极电极初始化为初始化电压电平。因此，可以改善初始化特性以增强响应特性和亮度的劣化，并且可以补偿驱动晶体管的阈值电压 (Tdr) 和高电位电压端子处的纹波的出现。

$$I_{OLED} = k \cdot (V_{dd} - V_{data})^2 \quad (1)$$